
Good Transient Response Low Voltage 500 mA LDO for High Temperature Applications*

NO.EA-375-200904

OUTLINE

The RP111x is a CMOS-based LDO regulator featuring 500 mA output current. The input voltage is as low as 1.4 V and the output voltage can be set from 0.7 V. Due to a built-in 0.46 Ω (at $V_{OUT} = 2.8$ V) on-resistor, RP111x can provide a low dropout voltage. RP111x also features an excellent line transient response, ripple rejection at 75 dB, and low noise. The output voltage accuracy is as high as ±0.8% and the temperature drift coefficient of output voltage is low at ±30 ppm/°C. The accuracy of the output voltage of RP111x includes the temperature characteristics and the load transient response has been improved. The typ. and max value of under/overshoot for various output current are shown in the typical characteristics, therefore the accuracy of the output voltage estimation will be easy on the actual operating cases. In addition to a fold-back protection circuit built into conventional regulators, RP111x contains a thermal shutdown circuit and an inrush current limit circuit.

SOT-23-5, SOT-89-5, and DFN1212-6 packages are available.

* This product is a high-reliability semiconductor device that is designed for the use in high-temperature environment. This product has successfully passed our rigorous reliability test in addition to the high-temperature test. To distinguish this product from our consumer products, "-Yx" is added to the end of the name of the product.

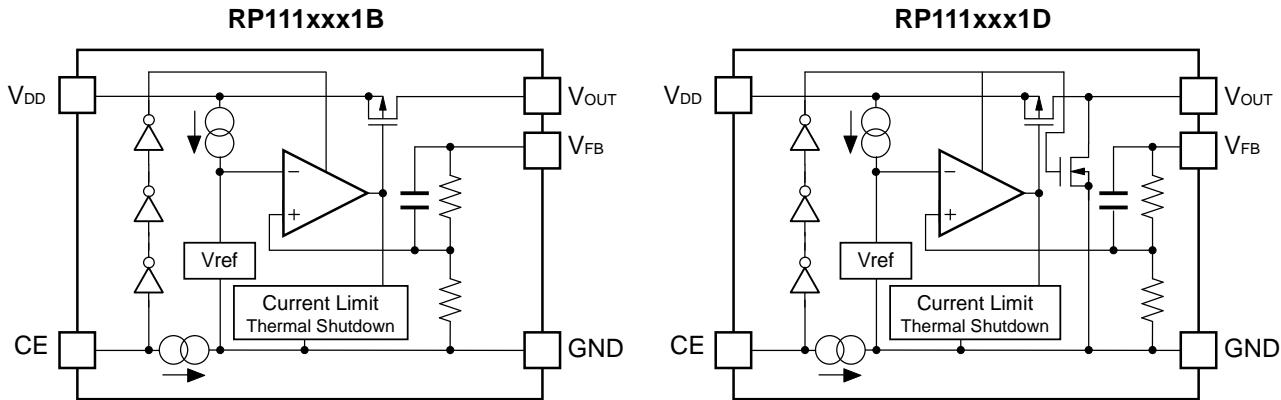
FEATURES

- Input Voltage Range (Maximum Rating)..... 1.4 V to 5.25 V (6.0 V)
- Operating Temperature -40°C to 105°C
- Supply Current Typ. 80 μA
- Standby Current Typ. 0.1 μA
- Dropout Voltage Typ. 0.23 V ($I_{OUT} = 500$ mA, $V_{SET} = 2.5$ V)
- Ripple Rejection Typ. 75 dB ($f = 1$ kHz)
Typ. 70 dB ($f = 10$ kHz)
- Output Voltage Accuracy ±0.8% ($V_{SET} \geq 1.8$ V)
- Output Voltage Temperature Coefficient Typ. ±30 ppm/°C ($V_{SET} \geq 1.8$ V)
- Line Regulation Typ. 0.02%/V
- Input Transient Response Typ. ±1.5 mV ($V_{IN}: V_{SET} + 0.5$ V ↔ $V_{SET} + 1.5$ V ($t_r = t_f = 5.0$ μs),
 $V_{IN} \geq 1.4$ V, $I_{OUT} = 30$ mA)
- Packages DFN1212-6, SOT-23-5, SOT-89-5
- Output Voltage Range 0.7 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 2.7 V, 2.8 V, 3.0 V, 3.3 V, 3.4 V
Contact our company sales representatives for other voltages.
- Built-in Fold-back Protection Circuit Typ. 50 mA
- Thermal Shutdown Temperature 165°C
- Inrush Current Limit Typ. 400 mA (for 180 μs after start-up)
- Ceramic capacitors are recommended to be used with this IC 1.0 μF or more
- Output Noise $20 \times V_{SET}$ μVrms (BW = 10 Hz to 100 kHz, $V_{SET} \geq 1.8$ V)

APPLICATIONS

- Industrial equipments such as FAs and smart meters
- Equipments used under high-temperature conditions
- Equipments accompanied by self-heating

BLOCK DIAGRAMS



SELECTION GUIDE

The set output voltage, auto-discharge function,^{*1}, and package type for the IC are user-selectable.

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
RP111Lxx1*-TR-Y	DFN1212-6	5,000 pcs	Yes	Yes
RP111Nxx1*-TR-YE	SOT-23-5	3,000 pcs	Yes	Yes
RP111Hxx1*-T1-YE	SOT-89-5	1,000 pcs	Yes	Yes

xx: Specify the set output voltage (V_{SET})

0.7 V (07), 1.2 V (12), 1.5 V (15), 1.8 V (18), 2.5 V (25), 2.7 V (27), 2.8 V (28),
3.0 V (30), 3.3 V (33), 3.4 V (34)

Contact our company sales representatives for other voltages.

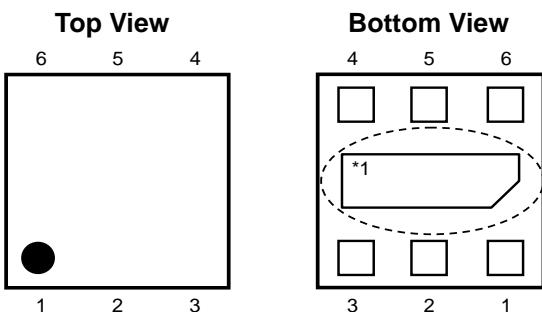
*: Specify the auto-discharge function at off state

- (B) Active-high, without auto discharge function at off state
- (D) Active-high, with auto discharge function at off state

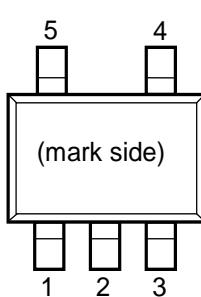
^{*1} Auto-discharge function quickly lowers the output voltage to 0 V by releasing the electrical charge in the external capacitor when the chip enable signal is switched from the active mode to the standby mode.

PIN DESCRIPTIONS

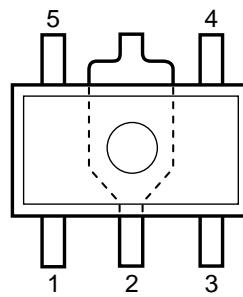
DFN1212-6



SOT-23-5



SOT-89-5



DFN1212-6

Pin No.	Symbol	Description
1	V_{OUT}	Output Pin
2	V_{FB}	Feed Back Pin
3	GND	Ground Pin
4	CE	Chip Enable Pin (Active-high)
5	NC	No connection
6	V_{DD}	Input Pin

*1 The tab on the bottom of the package enhances thermal performance and is electrically connected to GND (substrate level). It is recommended that the tab be connected to the ground plane on the board, or otherwise be left floating.

SOT-23-5

Pin No	Symbol	Description
1	V_{DD}	Input Pin
2	GND	Ground Pin
3	CE	Chip Enable Pin (Active-high)
4	V_{FB}	Feed Back Pin
5	V_{OUT}	Output Pin

SOT-89-5

Pin No	Symbol	Description
1	V_{FB}	Feed Back Pin
2	GND	Ground Pin
3	CE	Chip Enable Pin (Active-high)
4	V_{DD}	Input Pin
5	V_{OUT}	Output Pin

The V_{OUT} pin should be connected to the V_{FB} pin when using RP111x as an internal fixed output voltage type. In case of using this device as an external adjustable type, refer to *ADJUSTABLE OUTPUT VOLTAGE SETTING* for detailed information.

ABSOLUTE MAXIMUM RATINGS

Symbol	Item	Rating	Unit
V _{IN}	Input Voltage	−0.3 to 6.0	V
V _{CE}	Input Voltage (CE Pin)	−0.3 to 6.0	V
V _{OUT}	Output Voltage	−0.3 to V _{IN} + 0.3	V
I _{OUT}	Output Current	510	mA
P _D	Power Dissipation (DFN1212-6) ^{*1}	600	mW
	Power Dissipation (SOT-23-5) ^{*1}	420	
	Power Dissipation (SOT-89-5) ^{*1}	900	
	High Wattage Land Pattern	1300	
T _j	Junction Temperature	−40 to 125	°C
T _{stg}	Storage Temperature	−55 to 125	°C

^{*1} Refer to PACKAGE INFORMATION for detailed information.

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Rating	Unit
V _{IN}	Input Voltage ^{*2}	1.4 to 5.25	V
T _a	Operating Temperature	−40 to 105	°C

^{*2} In case of exceeding the maximum Input Voltage of 5.25 V, the device must be operated on condition that the Input Voltage is up to 5.5 V and the total operating time is within 500 hrs.

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

ELECTRICAL CHARACTERISTICS

$V_{IN} = V_{SET} + 1.0 \text{ V}$ ($V_{SET} > 1.5 \text{ V}$), $V_{IN} = 2.5 \text{ V}$ ($V_{SET} \leq 1.5 \text{ V}$), $I_{OUT} = 1 \text{ mA}$,

$C_{IN} = C_{OUT} = 1.0 \mu\text{F}$, unless otherwise noted.

The specifications surrounded by are guaranteed by design engineering at $-40^\circ\text{C} \leq Ta \leq 105^\circ\text{C}$.

RP111xxx1D/B

($T_a = 25^\circ\text{C}$)

Symbol	Item	Conditions		Min.	Typ.	Max.	Unit
V_{OUT}	Output voltage	$T_a = 25^\circ\text{C}$	$V_{SET} \geq 1.8 \text{ V}$	x 0.992		x 1.008	V
			$V_{SET} < 1.8 \text{ V}$	-18		18	mV
		$-40^\circ\text{C} \leq Ta \leq 105^\circ\text{C}$	$V_{SET} \geq 1.8 \text{ V}$	x 0.985		x 1.015	V
			$V_{SET} < 1.8 \text{ V}$	-55		50	mV
I_{OUT}	Output Current			500			mA
$\Delta V_{OUT}/\Delta I_{OUT}$	Load regulation	$1 \text{ mA} \leq I_{OUT} \leq 500 \text{ mA}$			1	20	mV
V_{TRLD}	Load Transient Response	$I_{OUT}: 1 \text{ mA} \leftrightarrow 250 \text{ mA}$ $(tr = tf = 0.5 \mu\text{s})$	$C_{OUT} = 1 \mu\text{F}$		-75 +45		mV
			$C_{OUT} = 2.2 \mu\text{F}$		-55 +35		
		$I_{OUT}: 1 \text{ mA} \leftrightarrow 250 \text{ mA}$ $(tr = tf = 5 \mu\text{s})$	$C_{OUT} = 1 \mu\text{F}$		-20 +15		
V_{DIF}	Dropout Voltage	Refer to the <i>Dropout Voltage</i>					
I_{SS}	Supply Current	$I_{OUT} = 0 \text{ mA}$			80	125	μA
$I_{standby}$	Standby Current	$V_{CE} = 0 \text{ V}$			0.1	7.0	μA
$\Delta V_{OUT}/\Delta V_{IN}$	Line regulation	$V_{SET} + 0.5 \text{ V} \leq V_{IN} \leq 5.25 \text{ V}$, $V_{IN} \geq 1.4 \text{ V}$			0.02	0.10	%/V
I_{SC}	Short Current Limit	$V_{OUT} = 0 \text{ V}$			50		mA
I_{PD}	CE Pull-down Current				0.3	0.6	μA
V_{CEH}	CE Input Voltage "H"			1.0			V
V_{CEL}	CE Input Voltage "L"					0.4	V
T_{TSD}	Thermal Shutdown Temperature	Junction Temperature			165		$^\circ\text{C}$
T_{TSR}	Thermal Shutdown Released Temperature	Junction Temperature			100		$^\circ\text{C}$
R_{LOW}	LOW output Nch Tr. ON Resistance (RP111xxx1D only)	$V_{IN} = 4.0 \text{ V}$, $V_{CE} = 0 \text{ V}$			60		Ω

All test items listed under Electrical Characteristics are done under the pulse load condition ($T_j \approx Ta = 25^\circ\text{C}$) except for Load Transient Response.

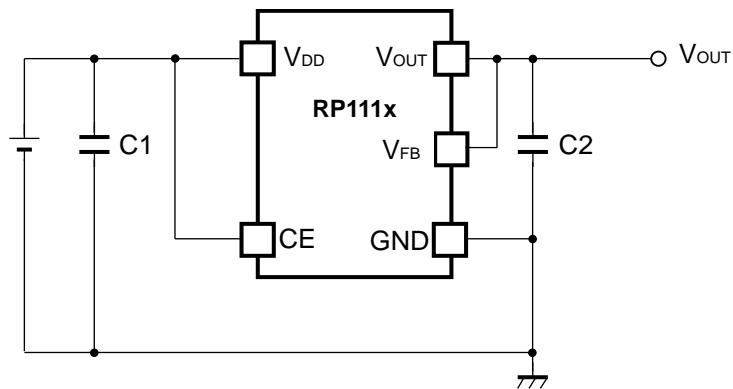
The specifications surrounded by are guaranteed by design engineering at $-40^{\circ}\text{C} \leq \text{Ta} \leq 105^{\circ}\text{C}$.

Dropout Voltage

(Ta = 25°C)

Output Voltage $V_{\text{OUT}} (\text{V})$	Dropout Voltage $V_{\text{DIF}} (\text{V})$		
	Condition	Typ.	Max.
0.7 ≤ $V_{\text{SET}} < 0.8$	$I_{\text{OUT}} = 500 \text{ mA}$	0.58	<input type="checkbox"/> 0.88
0.8 ≤ $V_{\text{SET}} < 0.9$		0.52	<input type="checkbox"/> 0.80
0.9 ≤ $V_{\text{SET}} < 1.0$		0.45	<input type="checkbox"/> 0.70
1.0 ≤ $V_{\text{SET}} < 1.2$		0.42	<input type="checkbox"/> 0.64
1.2 ≤ $V_{\text{SET}} < 1.4$		0.35	<input type="checkbox"/> 0.53
1.4 ≤ $V_{\text{SET}} < 1.8$		0.31	<input type="checkbox"/> 0.48
1.8 ≤ $V_{\text{SET}} < 2.1$		0.27	<input type="checkbox"/> 0.44
2.1 ≤ $V_{\text{SET}} < 2.5$		0.25	<input type="checkbox"/> 0.38
2.5 ≤ $V_{\text{SET}} < 3.0$		0.23	<input type="checkbox"/> 0.34
3.0 ≤ $V_{\text{SET}} \leq 3.6$		0.22	<input type="checkbox"/> 0.32

TYPICAL APPLICATION



External Components

C1, C2: Ceramic Capacitor 1.0 μF Murata GRM155B31A105KE15

TECHNICAL NOTES

Phase Compensation

In this device, phase compensation is made for securing stable operation even if the load current is varied. For this purpose, use a 1.0 μF or more capacitor C2.

In case of using a tantalum capacitor, and its ESR is large, the output may be unstable. Therefore, select C2 carefully considering its frequency characteristics.

When using the Adjustable Output Voltage Type, set 4.7 μF or more of the output capacitor C2 as close as possible to the device, and make wiring as short as possible.

PCB Layout

Make V_{DD} and GND lines sufficient. If their impedance is high, noise pickup or unstable operation may result.

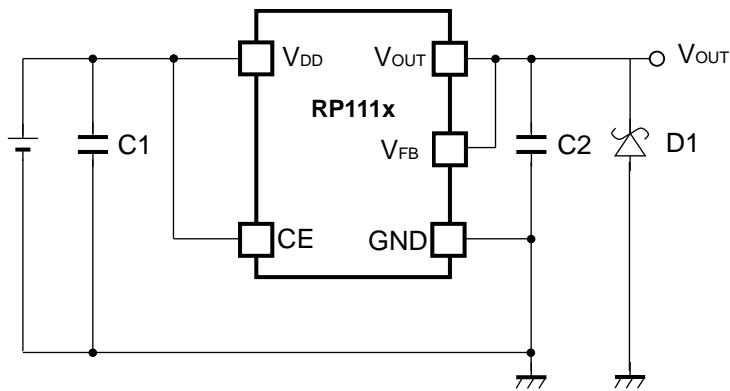
Connect a capacitor C1 with a capacitance value as much as 1.0 μF or more between V_{DD} and GND pin, and as close as possible to the pins.

Set external components, especially the output capacitor C2, as close as possible to the device, and make wiring as short as possible (Refer to *TYPICAL APPLICATION*).

Transient Response

When using the Adjustable Output Voltage Type, the transient response could be affected by the external resistors. Evaluate the circuit taking the actual conditions of use into account.

TYPICAL APPLICATION FOR IC CHIP BREAKDOWN PREVENTION



When a sudden surge of electrical current travels along the V_{OUT} pin and GND due to a short-circuit, electrical resonance of a circuit involving an output capacitor (C2) and a short circuit inductor generates a negative voltage and may damage the device or the load devices. Connecting a schottky diode (D1) between the V_{OUT} pin and GND has the effect of preventing damage to them.

ADJUSTABLE OUTPUT VOLTAGE SETTING

Output Voltage Setting

RP111x is capable of adjusting the output voltage by using the external divider resistors. If the V_{FB} voltage fixed in the device is described as $\text{set}V_{FB}$, the output voltage can be set by using the following formulas.

Thus,

$$I_{11} = I_{IC} + \text{setV}_{FB} / R_2 \dots \quad (3)$$

Therefore,

$$V_{OUT} = setV_{FB} + R1 \times I1 \quad \dots \quad (4)$$

Put formula (3) into formula (4), then

In formula (5), $R1 \times I_{IC}$ is the error-causing factor in V_{OUT} .

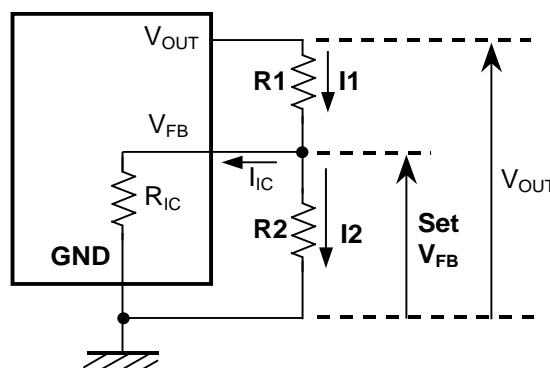
As for I_{IC} ,

Therefore, the error-causing factor $R1x I_{IC}$ can be described as follows.

$$R1 \times I_{IC} = R1 \times \frac{setV_{FB}}{R_{IC}} \\ = setV_{FB} \times R1 / R_{IC} (7)$$

For better accuracy, choosing R1 ($\ll R_{IC}$) reduces this error.

Without the error-causing factor $R_{1x} I_{IC}$, the output voltage can be calculated by the following formula.



The output voltage of the externally adjustable output voltage type should be set to 3.6 V or less.

The resistance of R2 should be 16 k Ω or less.

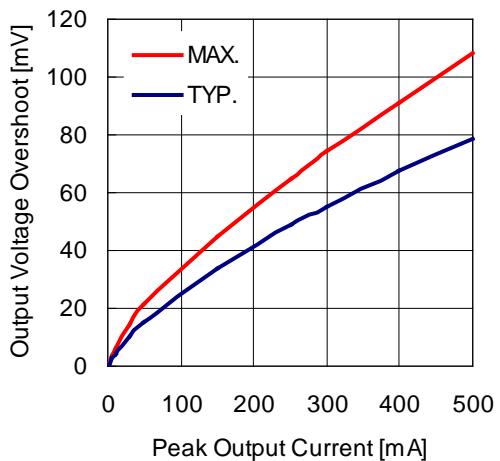
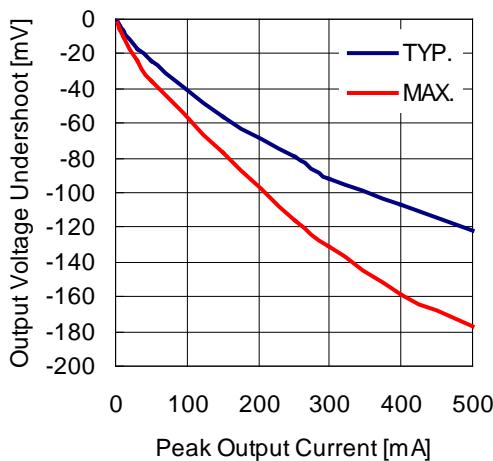
TRANSIENT RESPONSE

The RP111x has been improved in overall output voltage characteristics including temperature and transient response. The load transient response indicated under the Electrical Characteristics is guaranteed by design based on the condition when I_{OUT} changes from 1 mA to 250 mA or 250 mA to 1 mA. The output voltage variations under the other load conditions, the characteristic examples are shown below.

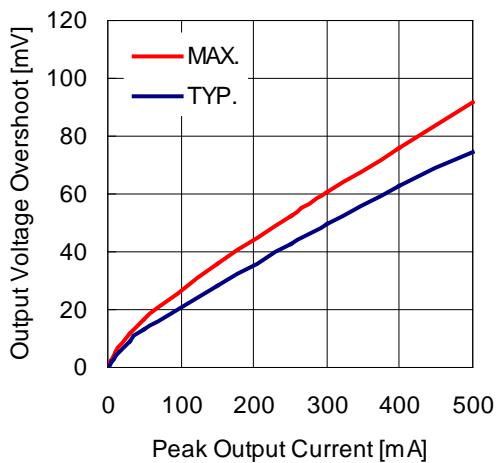
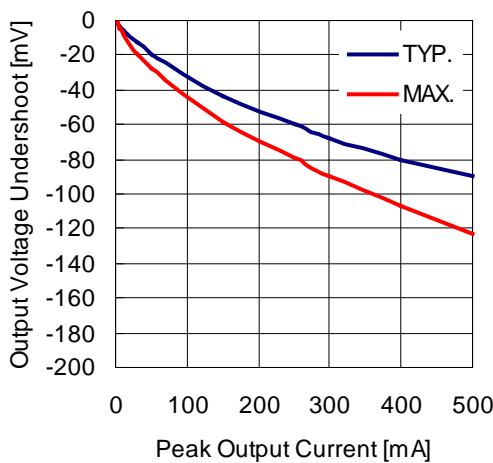
RP111x151x

$V_{IN} = 2.5$ V, $-40^\circ\text{C} \leq Ta \leq 85^\circ\text{C}$

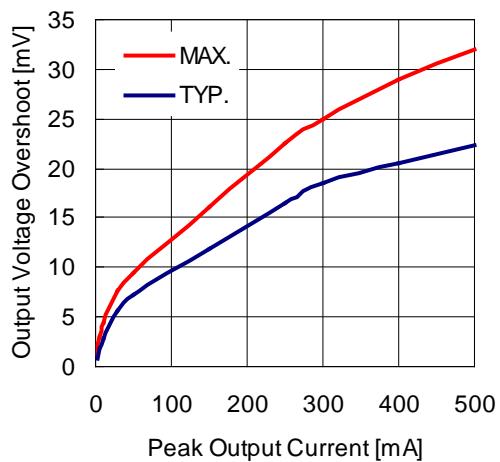
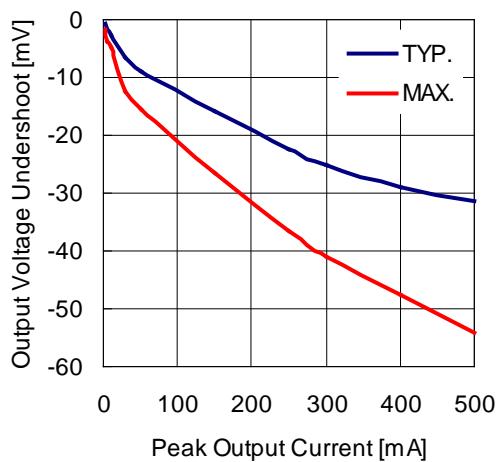
$C_{IN} = 1.0 \mu\text{F}$, $C_{OUT} = 1.0 \mu\text{F}$, $I_{OUT} = 1 \text{ mA} \Leftrightarrow$ Peak Output Current



$C_{IN} = 1.0 \mu\text{F}$, $C_{OUT} = 2.2 \mu\text{F}$, $I_{OUT} = 1 \text{ mA} \Leftrightarrow$ Peak Output Current



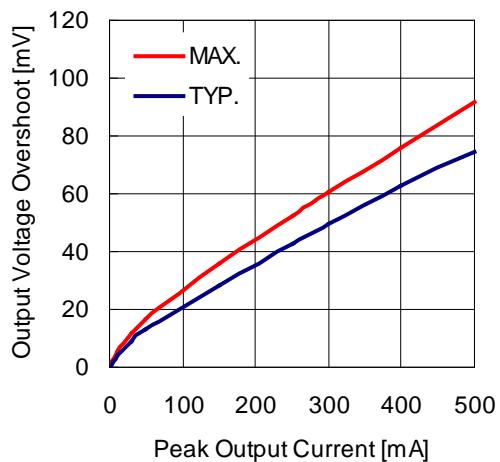
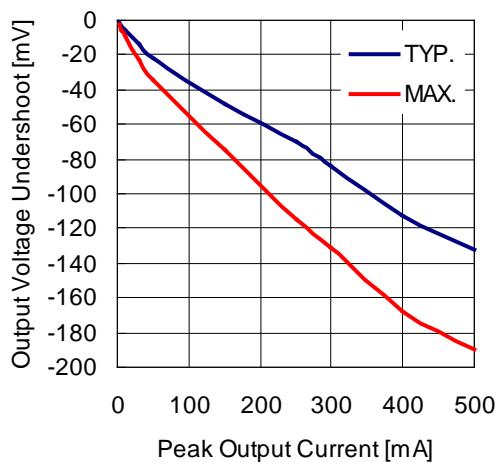
$C_{IN} = 1.0 \mu F, C_{OUT} = 1.0 \mu F, I_{OUT} = 1 \text{ mA} \Leftrightarrow \text{Peak Output Current}$



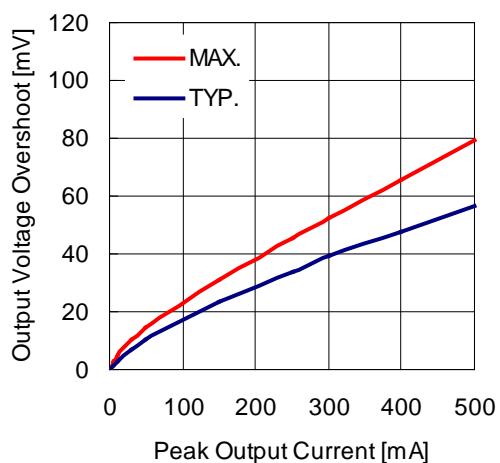
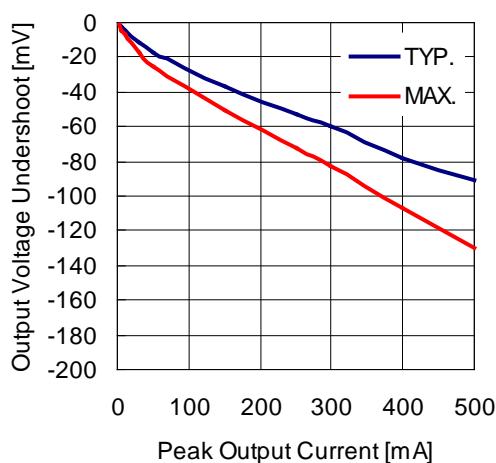
RP111x281x

$V_{IN} = 3.8 \text{ V}, -40^\circ\text{C} \leq Ta \leq 85^\circ\text{C}$

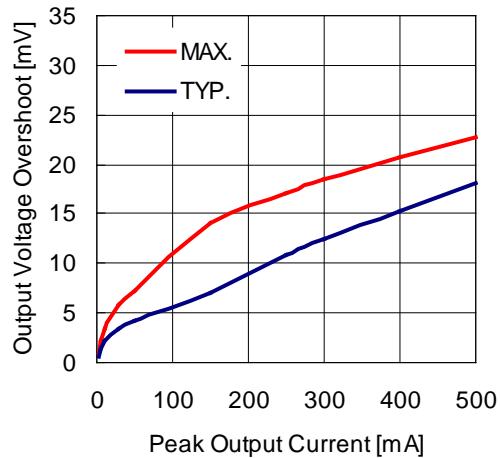
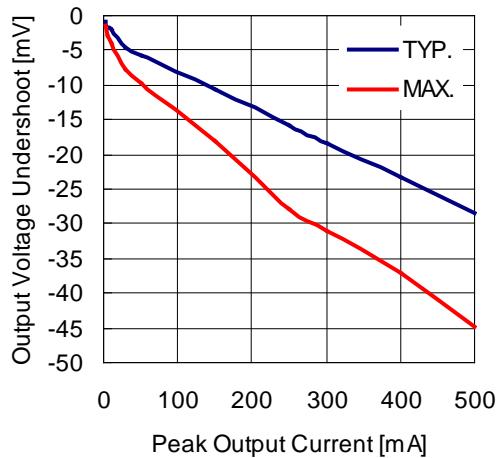
$C_{IN} = 1.0 \mu F, C_{OUT} = 1.0 \mu F, I_{OUT} = 1 \text{ mA} \Leftrightarrow \text{Peak Output Current}$



$C_{IN} = 1.0 \mu F, C_{OUT} = 2.2 \mu F, I_{OUT} = 1 \text{ mA} \Leftrightarrow \text{Peak Output Current}$

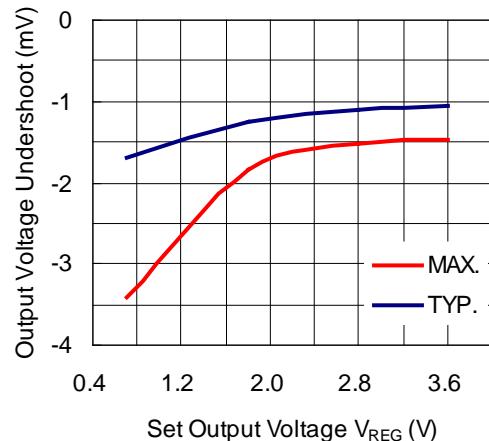
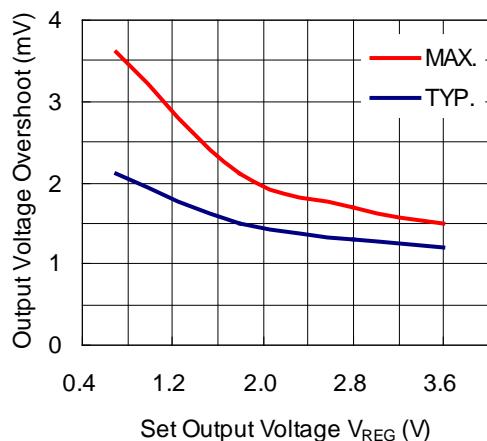


$C_{IN} = 1.0 \mu F$, $C_{OUT} = 1.0 \mu F$, $I_{OUT} = 1 \text{ mA} \Leftrightarrow$ Peak Output Current



Input Transient Response has the output voltage dependency. Please refer to the characteristic examples below.

$V_{IN}: V_{SET} + 0.5 \text{ V} \Leftrightarrow V_{SET} + 1.5 \text{ V}$ ($t_r = t_f = 5.0 \mu\text{s}$), $V_{IN} \geq 1.4 \text{ V}$,
 $C_{OUT} = 1.0 \mu F$, $I_{OUT} = 30 \text{ mA}$



The graphs shown above are reference data.

For the better transient response, a capacitor with higher capacitance is recommended and the wire impedance of GND and V_{OUT} should be minimized as possible.

The transient response characteristics depend on the external parts and PCB layout. Therefore, the operating conditions for the transient response in the application should be considered and evaluation is necessary.

PACKAGE INFORMATION

POWER DISSIPATION (DFN1212-6)

Power Dissipation (P_D) depends on conditions of mounting on board. This specification is based on the measurement at the condition below:

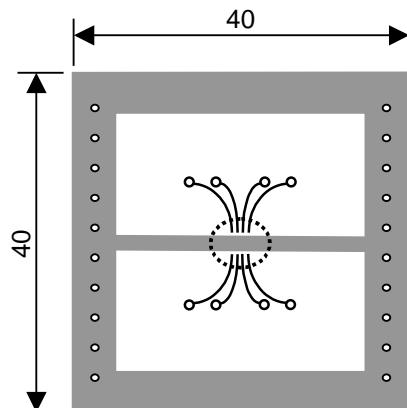
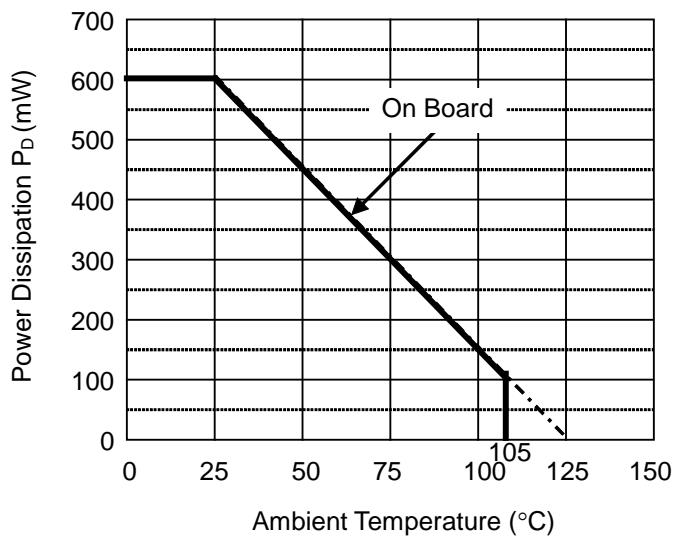
Measurement Conditions

	Standard Test Land Pattern
Environment	Mounting on Board (Wind velocity = 0 m/s)
Board Material	Glass cloth epoxy plastic (Double sided)
Board Dimensions	40 mm*40 mm*1.6 mm
Copper Ratio	Top side: Approx. 50%, Back side: Approx. 50%
Through-holes	ϕ 0.5 mm * 28 pcs

Measurement Result

($T_a = 25^{\circ}\text{C}$, $T_{jmax} = 125^{\circ}\text{C}$)

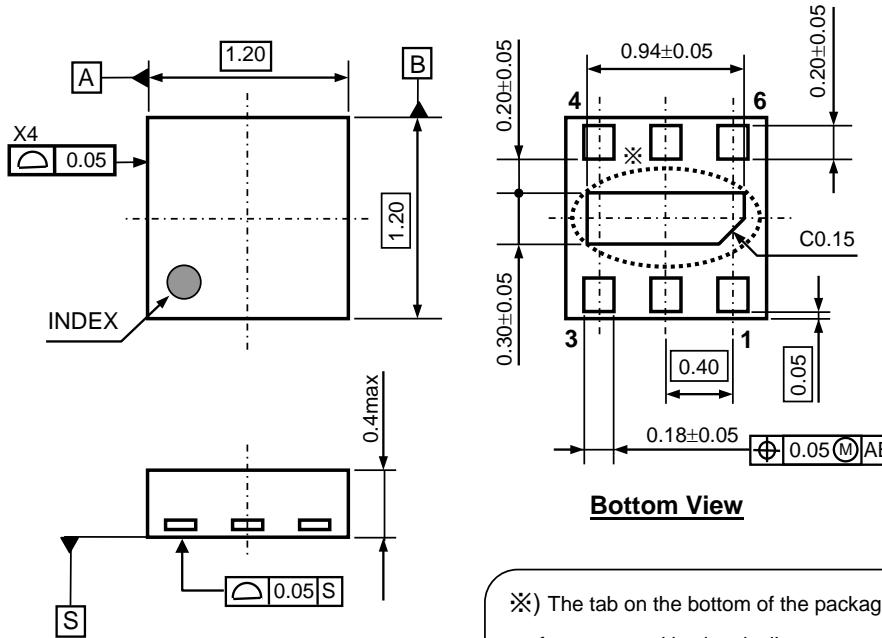
	Standard Test Land Pattern
Power Dissipation	600 mW
Thermal Resistance	$\theta_{ja} = (125-25^{\circ}\text{C})/0.6 \text{ W} = 167^{\circ}\text{C/W}$
	$\theta_{jc} = 30^{\circ}\text{C/W}$



Measurement Board Pattern

● IC Mount Area (Unit : mm)

PACKAGE DIMENSIONS (DFN1212-6)

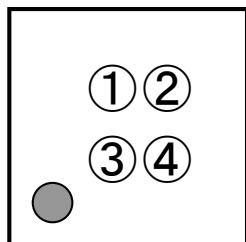


※) The tab on the bottom of the package enhances thermal performance and is electrically connected to GND (substrate level). It is recommended that the tab be connected to the ground plane on the board, or otherwise be left floating.

MARK SPECIFICATION (DFN1212-6)

①②: Product Code ... **Refer to MARK SPECIFICATION TABLE (DFN1212-6)**

③④: Lot Number ... Alphanumeric Serial Number



MARK SPECIFICATION TABLE (DFN1212-6)**RP111Lxx1B**

Product Name	① ②	V _{SET}
RP111L071B	7 A	0.7 V
RP111L121B	7 G	1.2 V
RP111L151B	7 L	1.5 V
RP111L181B	7 P	1.8 V
RP111L251B	7 X	2.5 V
RP111L271B	7 Z	2.7 V
RP111L281B	8 A	2.8 V
RP111L301B	8 D	3.0 V
RP111L331B	8 G	3.3 V
RP111L341B	8 H	3.4 V

RP111Lxx1D

Product Name	① ②	V _{SET}
RP111L071D	9 A	0.7 V
RP111L121D	9 G	1.2 V
RP111L151D	9 L	1.5 V
RP111L181D	9 P	1.8 V
RP111L251D	9 X	2.5 V
RP111L271D	9 Z	2.7 V
RP111L281D	0 A	2.8 V
RP111L301D	0 D	3.0 V
RP111L331D	0 G	3.3 V
RP111L341D	0 H	3.4 V

POWER DISSIPATION (SOT-23-5)

Power Dissipation (P_D) depends on conditions of mounting on board. This specification is based on the measurement at the condition below (Power Dissipation (SOT-23-5) is substitution of SOT-23-6).

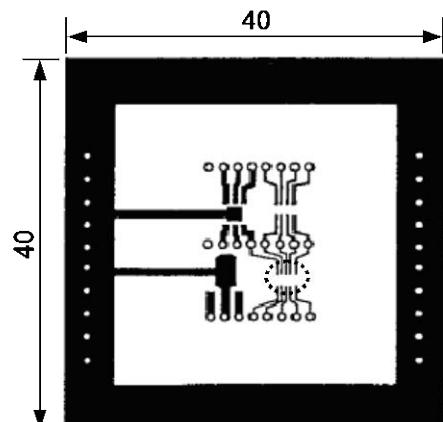
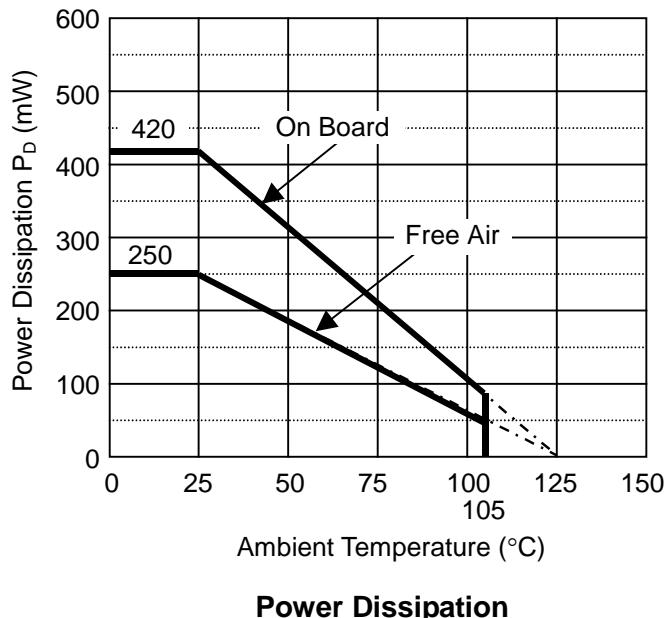
*** Measurement Conditions**

	Standard Test Land Pattern
Environment	Mounting on Board (Wind velocity = 0 m/s)
Board Material	Glass cloth epoxy plastic (Double sided)
Board Dimensions	40 mm*40 mm*1.6 mm
Copper Ratio	Top side: Approx. 50%, Back side: Approx. 50%
Through-holes	ϕ 0.5 mm * 44 pcs

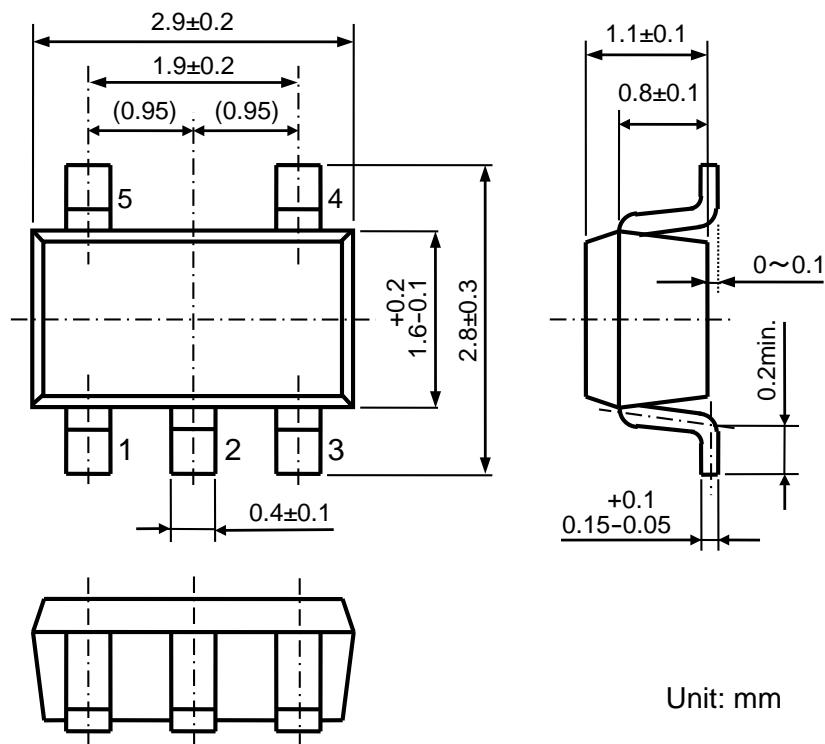
*** Measurement Result:**

(Ta = 25°C, Tjmax = 125°C)

	Standard Land Pattern	Free Air
Power Dissipation	420 mW	250 mW
Thermal Resistance	$\theta_{ja} = (125-25°C)/0.42 W = 238°C/W$	400°C/W

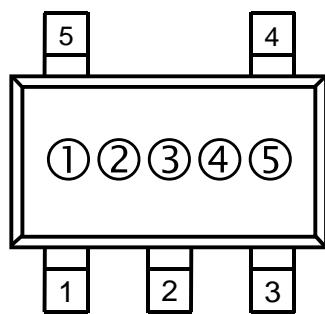
**Measurement Board Pattern**
IC Mount Area (Unit: mm)

PACKAGE DIMENSIONS (SOT-23-5)



MARK SPECIFICATION (SOT-23-5)

①②③: Product Code ... **Refer to MARK SPECIFICATION TABLE (SOT-23-5)**
④⑤: Lot Number ... Alphanumeric Serial Number



MARK SPECIFICATION TABLE (SOT-23-5)**RP111Nxx1B**

Product Name	①	②	③	V_{SET}
RP111N071B	H	0	7	0.7 V
RP111N121B	H	1	2	1.2 V
RP111N151B	H	1	5	1.5 V
RP111N181B	H	1	8	1.8 V
RP111N251B	H	2	5	2.5 V
RP111N271B	H	2	7	2.7 V
RP111N281B	H	2	8	2.8 V
RP111N301B	H	3	0	3.0 V
RP111N331B	H	3	3	3.3 V
RP111N341B	H	3	4	3.4 V

RP111Nxx1D

Product Name	①	②	③	V_{SET}
RP111N071D	J	0	7	0.7 V
RP111N121D	J	1	2	1.2 V
RP111N151D	J	1	5	1.5 V
RP111N181D	J	1	8	1.8 V
RP111N251D	J	2	5	2.5 V
RP111N271D	J	2	7	2.7 V
RP111N281D	J	2	8	2.8 V
RP111N301D	J	3	0	3.0 V
RP111N331D	J	3	3	3.3 V
RP111N341D	J	3	4	3.4 V

POWER DISSIPATION (SOT-89-5)

Power Dissipation (P_D) depends on conditions of mounting on board. This specification is based on the measurement at the condition below.

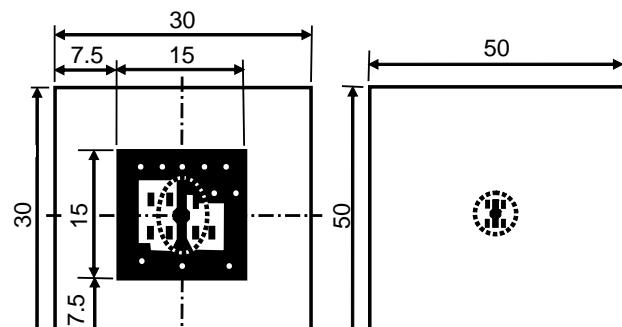
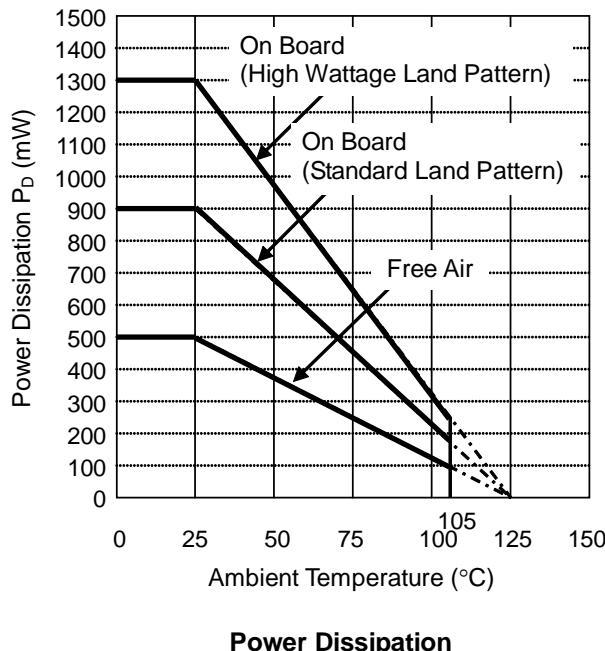
Measurement Conditions

	High Wattage Land Pattern	Standard Land Pattern
Environment	Mounting on Board (Wind velocity = 0 m/s)	Mounting on Board (Wind velocity = 0 m/s)
Board Material	Glass cloth epoxy plastic (Double sided)	Glass cloth epoxy plastic (Double sided)
Board Dimensions	30 mm × 30 mm × 1.6 mm	50 mm × 50 mm × 1.6 mm
Copper Ratio	Top side: Approx. 20%, Back side: Approx. 100%	Top side: Approx. 10%, Back side: Approx. 100%
Through-hole	φ0.85 mm × 10 pcs	-

Measurement Result

($T_a = 25^\circ\text{C}$, $T_{jmax} = 125^\circ\text{C}$)

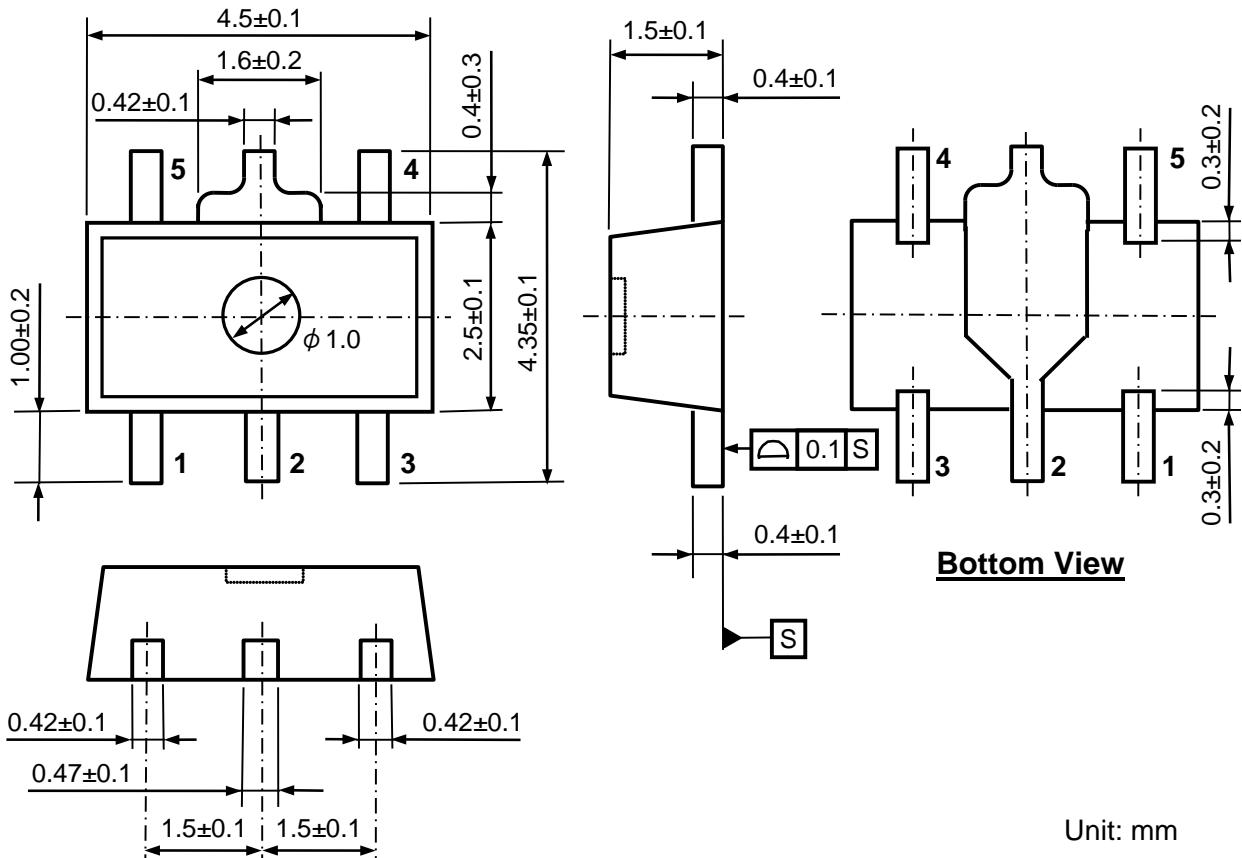
	High Wattage Land Pattern	Standard Land Pattern	Free Air
Power Dissipation	1300 mW	900 mW	500 mW
Thermal Resistance	77°C/W	111°C /W	200°C /W



Measurement Board Pattern



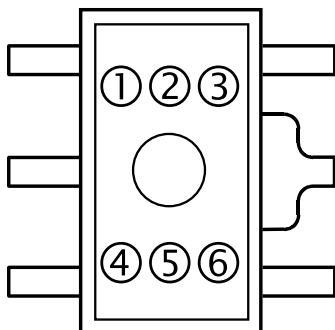
PACKAGE DIMENSIONS (SOT-89-5)



MARK SPECIFICATION (SOT-89-5)

①②③④: Product Code ... Refer to MARK SPECIFICATION TABLE (SOT-89-5)

⑤⑥: Lot Number ... Alphanumeric Serial Number



MARK SPECIFICATION TABLE (SOT-89-5)

RP111Hxx1B

Product Name	① ② ③ ④	V _{SET}
RP111H071B	A 0 7 B	0.7 V
RP111H121B	A 1 2 B	1.2 V
RP111H151B	A 1 5 B	1.5 V
RP111H181B	A 1 8 B	1.8 V
RP111H251B	A 2 5 B	2.5 V
RP111H271B	A 2 7 B	2.7 V
RP111H281B	A 2 8 B	2.8 V
RP111H301B	A 3 0 B	3.0 V
RP111H331B	A 3 3 B	3.3 V
RP111H341B	A 3 4 B	3.4 V

RP111Hxx1D

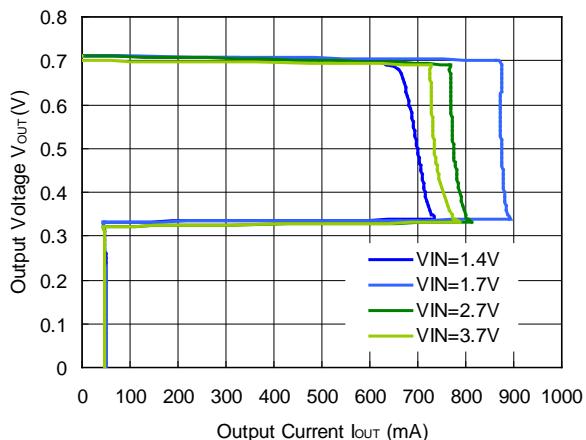
Product Name	① ② ③ ④	V _{SET}
RP111H071D	A 0 7 D	0.7 V
RP111H121D	A 1 2 D	1.2 V
RP111H151D	A 1 5 D	1.5 V
RP111H181D	A 1 8 D	1.8 V
RP111H251D	A 2 5 D	2.5 V
RP111H271D	A 2 7 D	2.7 V
RP111H281D	A 2 8 D	2.8 V
RP111H301D	A 3 0 D	3.0 V
RP111H331D	A 3 3 D	3.3 V
RP111H341D	A 3 4 D	3.4 V

■ 特性例

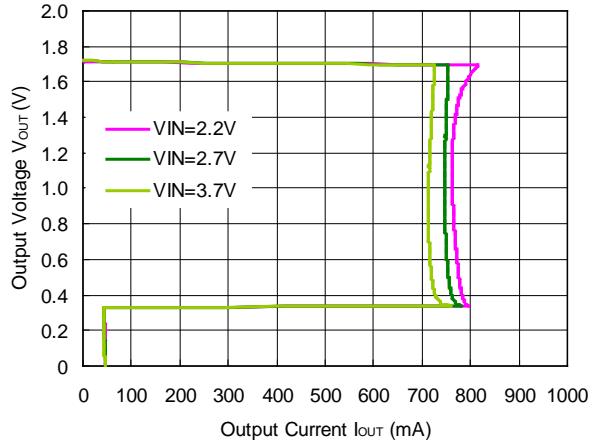
※以下の特性例は参考値であり、それぞれの値を保証するものではありません。

1) Output Voltage vs. Output Current (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, Ta = 25°C)

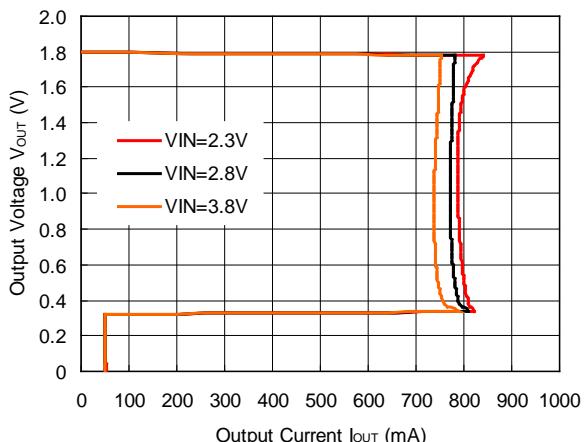
RP111x071x



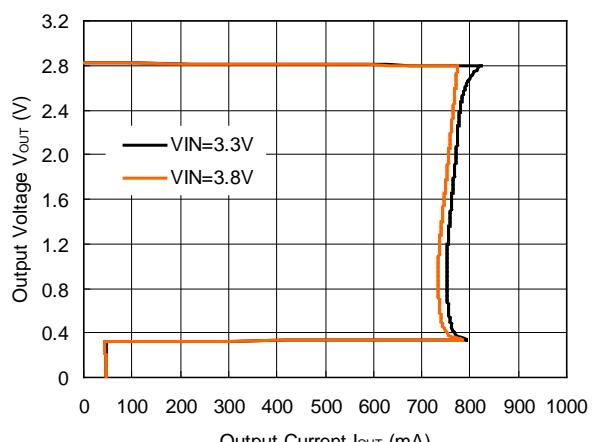
RP111x171x



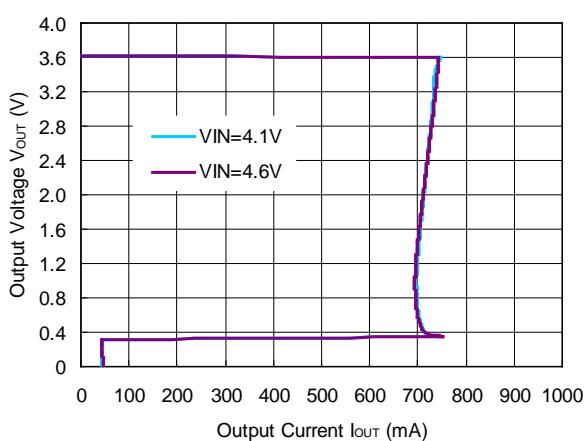
RP111x181x



RP111x281x

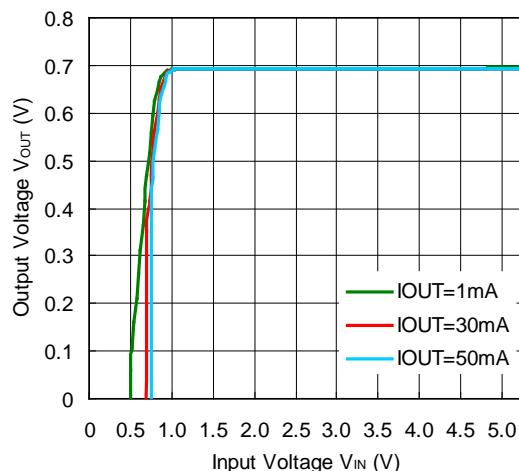


RP111x361x

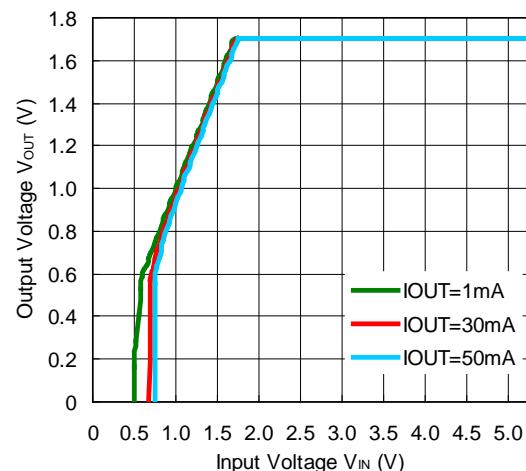


2) Output Voltage vs. Input Voltage (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, Ta = 25°C)

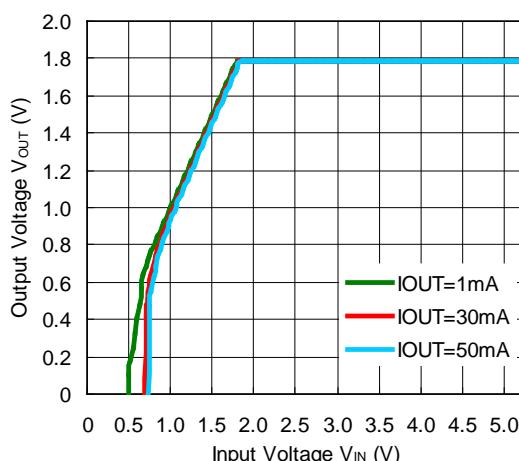
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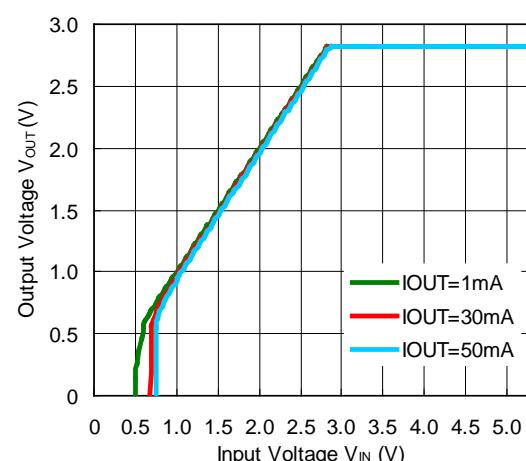
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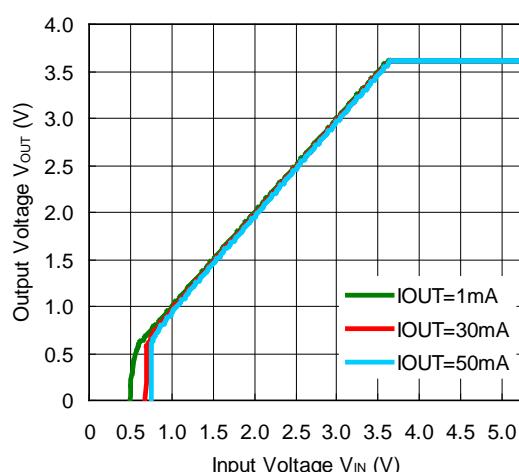
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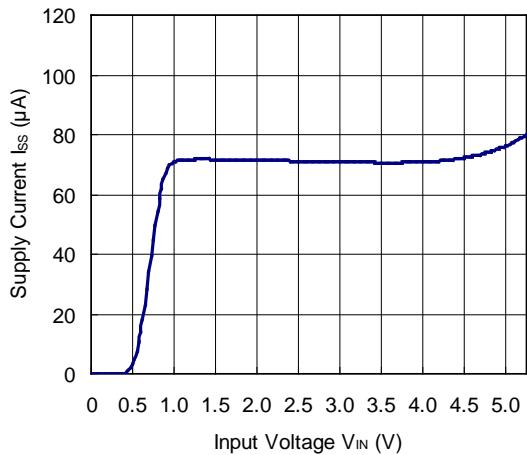
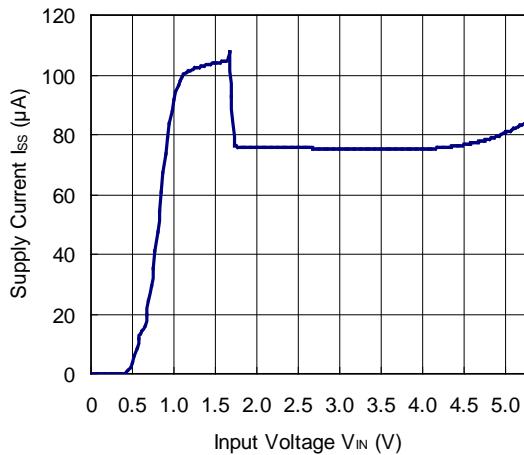
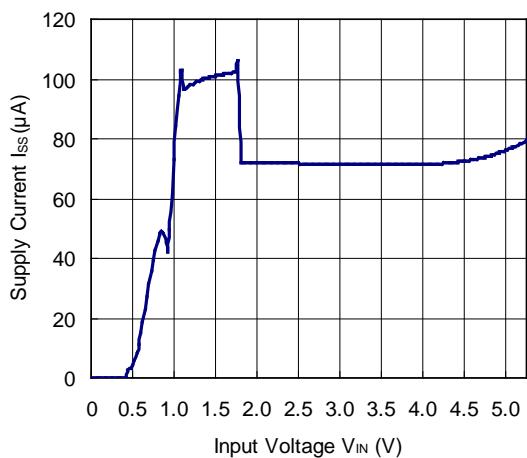
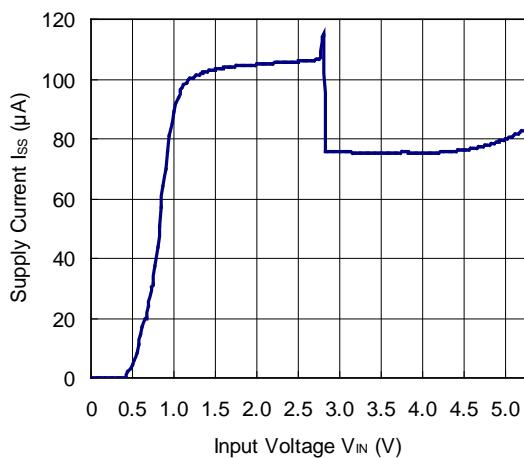
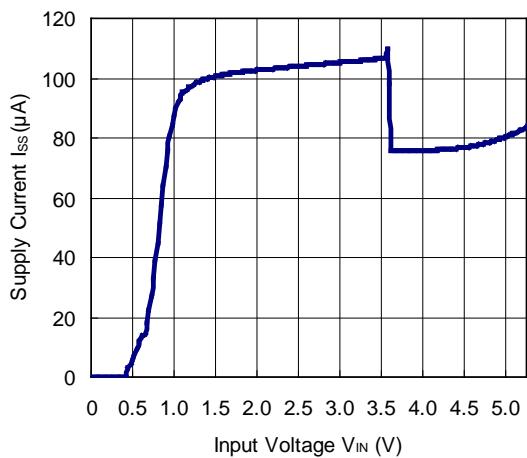


RP111x281x



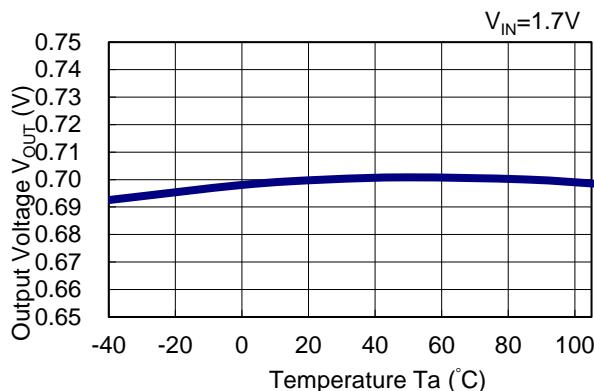
RP111x361x



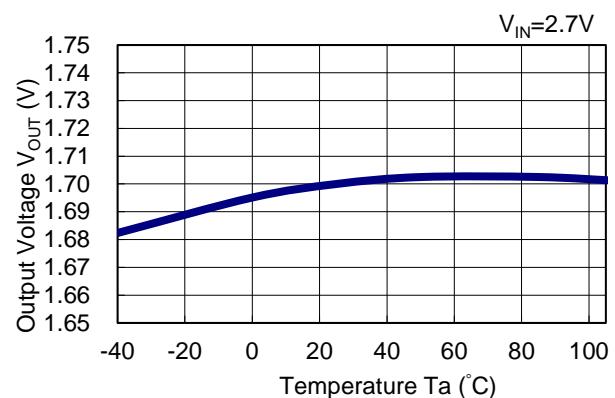
3) Supply Current vs. Input Voltage (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, Ta = 25°C)**RP111x071x****RP111x171x****RP111x181x****RP111x281x****RP111x361x**

4) Output Voltage vs. Temperature (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, I_{OUT} = 1 mA)

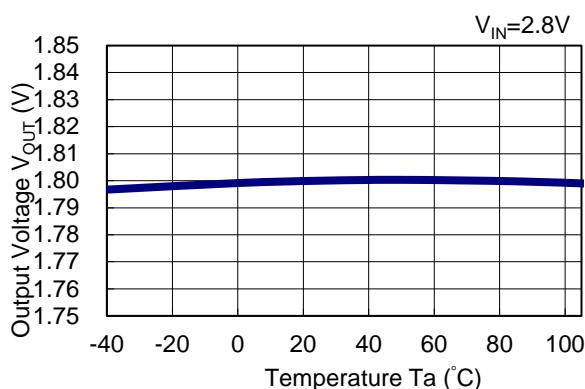
RP111x071x



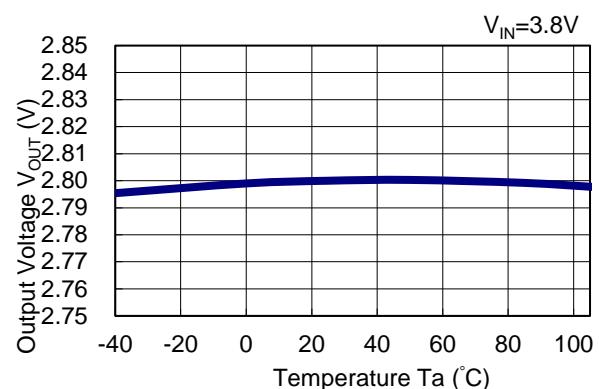
RP111x171x



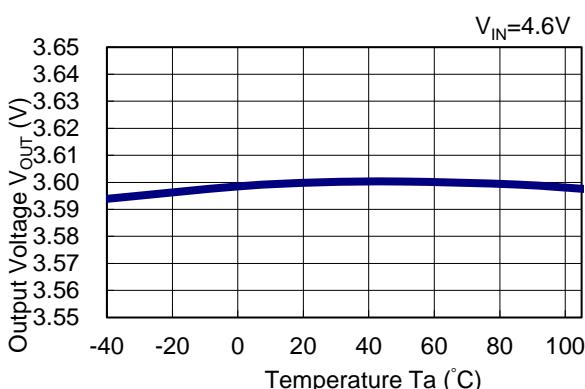
RP111x181x

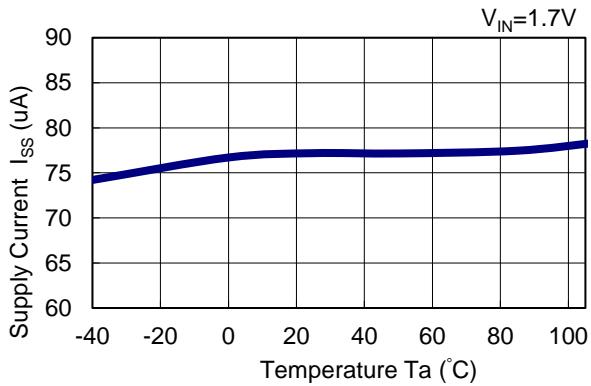
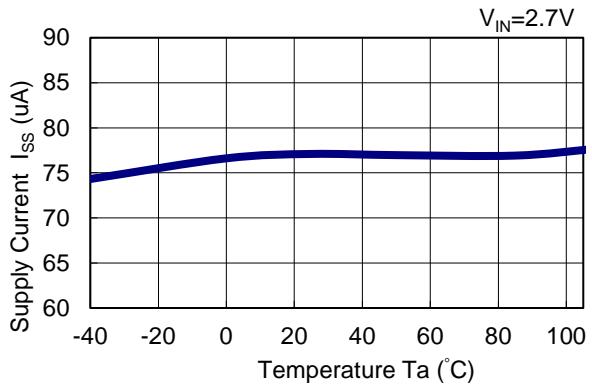
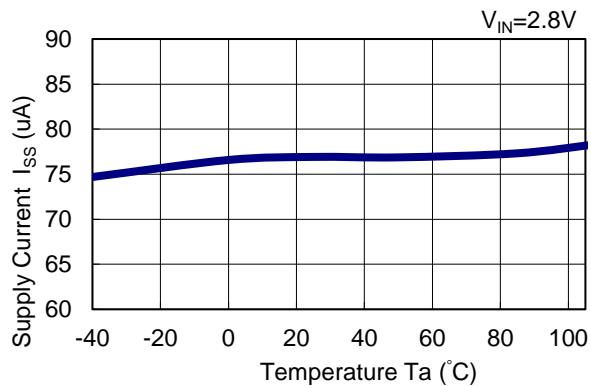
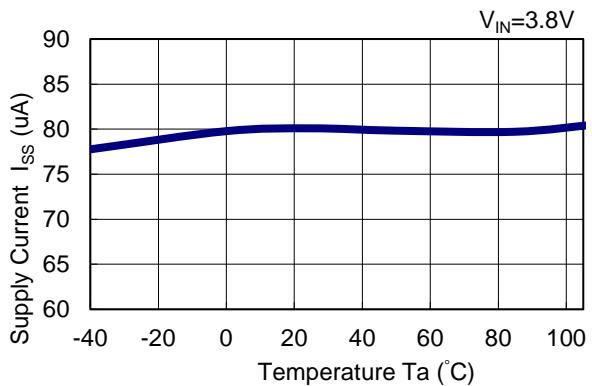
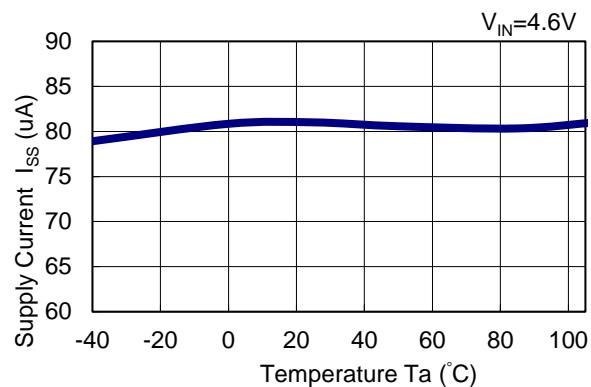


RP111x281x



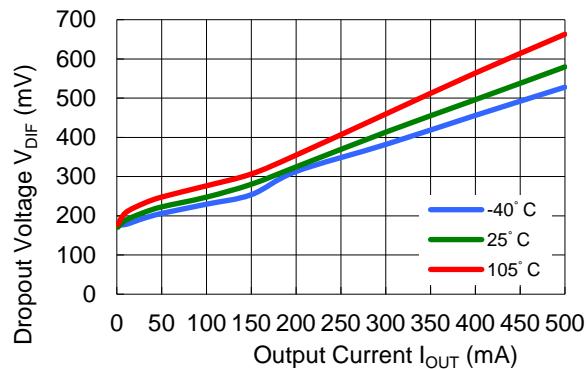
RP111x361x



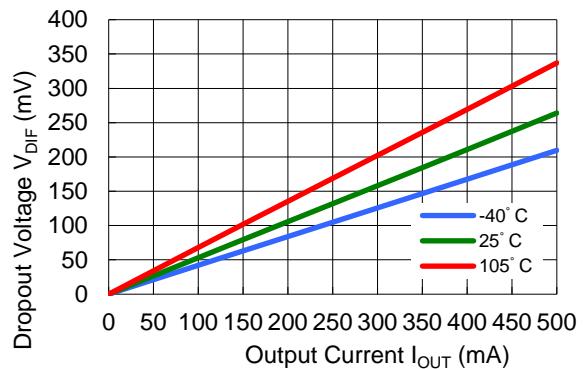
5) Supply Current vs. Temperature (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, $I_{OUT} = 0$ mA)**RP111x071x****RP111x171x****RP111x181x****RP111x281x****RP111x361x**

6) Dropout Voltage vs. Output Current (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F)

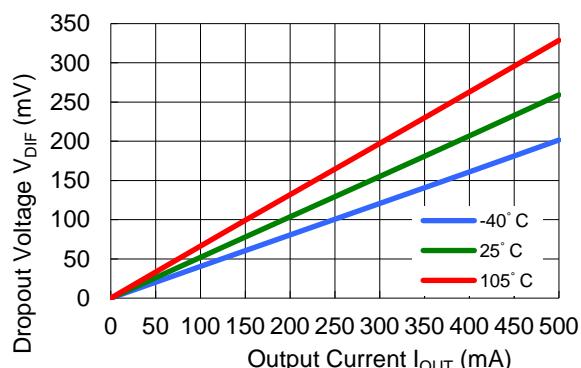
RP111x071x



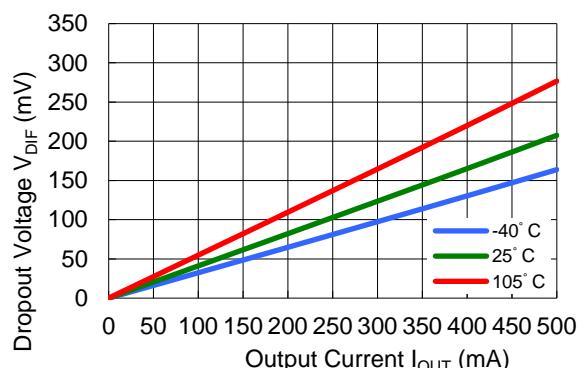
RP111x171x



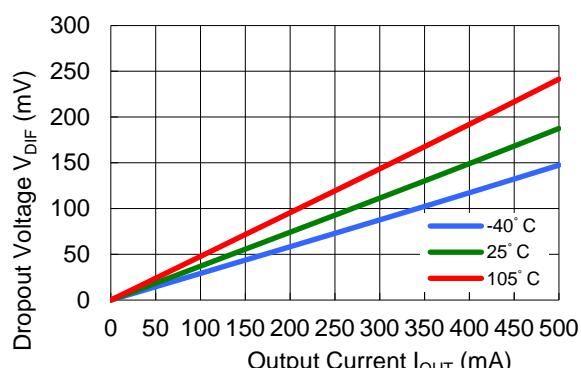
RP111x181x

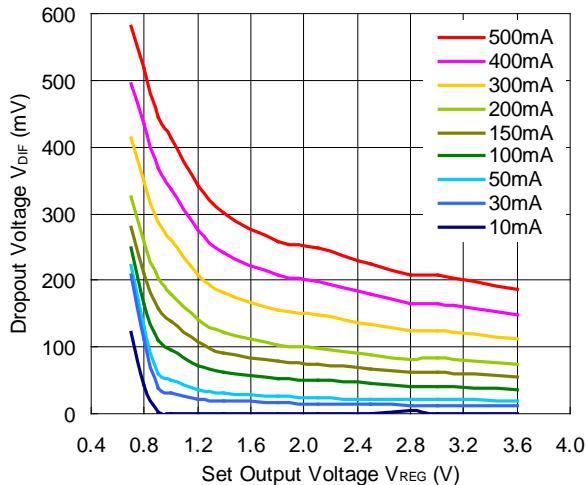
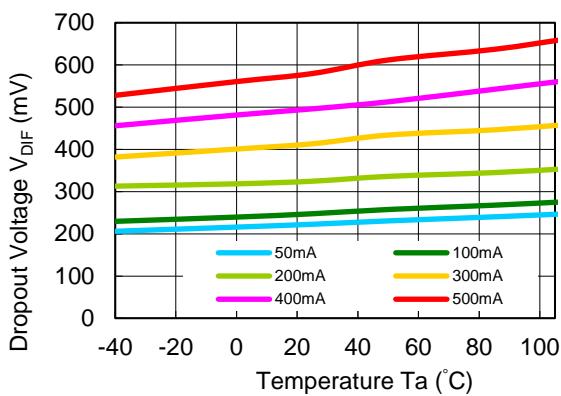
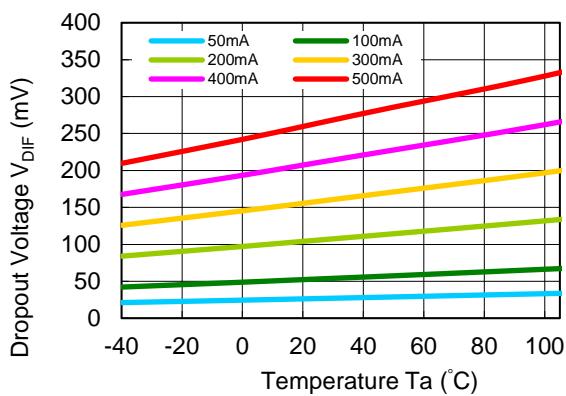
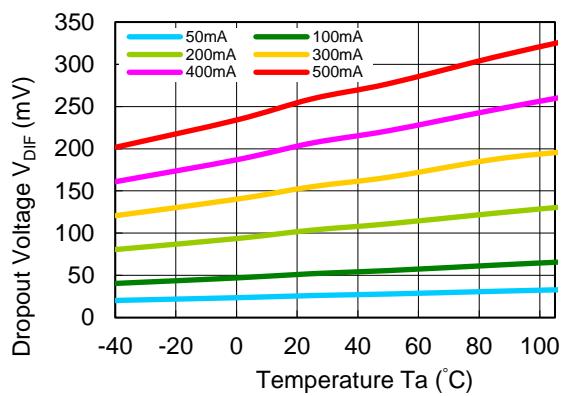
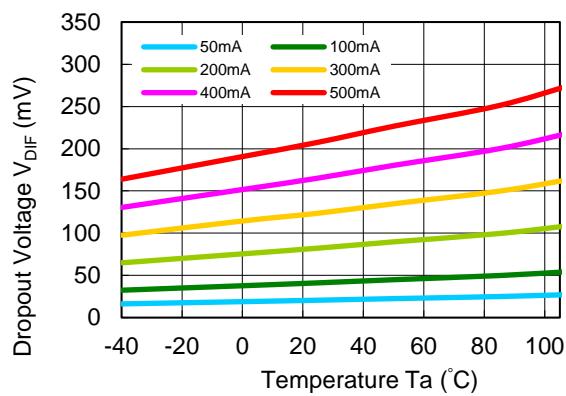


RP111x281x

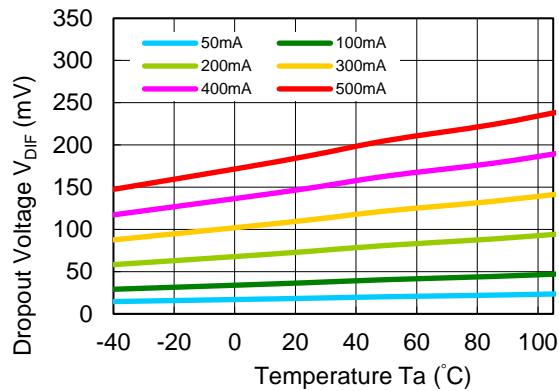


RP111x361x

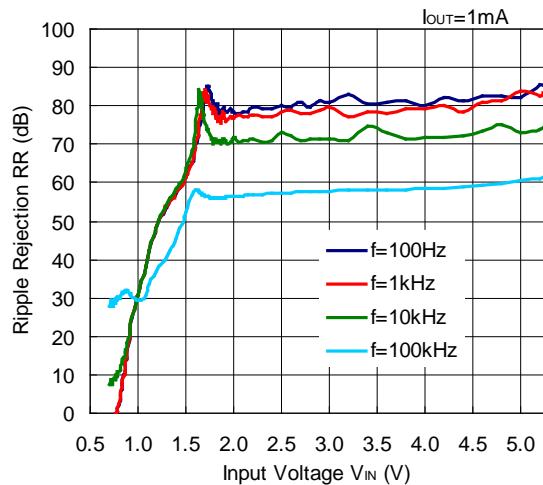


7) Dropout Voltage vs. Set Output Voltage (C1= Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, Ta = 25°C)**8) Dropout Voltage vs. Temperature (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F)****RP111x071x****RP111x171xx****RP111x181x****RP111x281x**

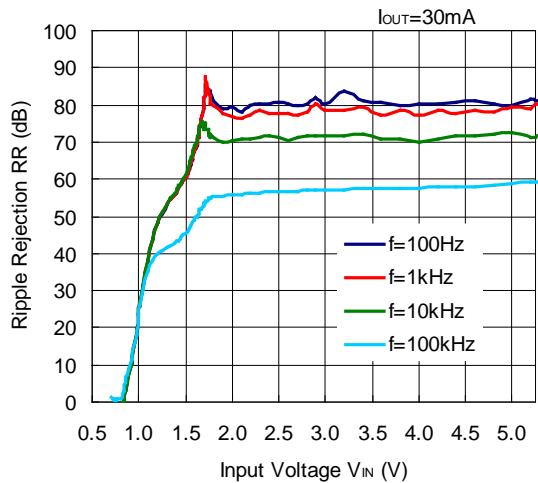
RP111x361x

9) Ripple Rejection vs. Input Voltage (C1 = none, C2 = Ceramic 1.0 μ F, Ripple = 0.2 V p-p, Ta = 25°C)

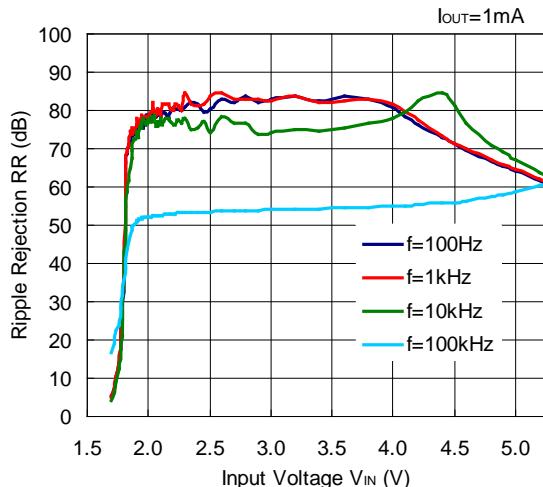
RP111x071x



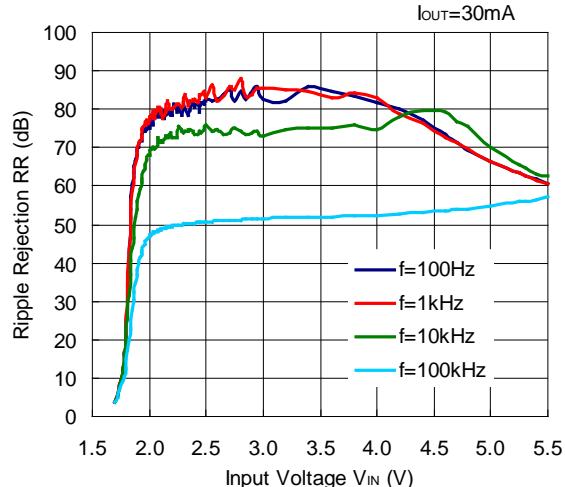
RP111x071x



RP111x171x



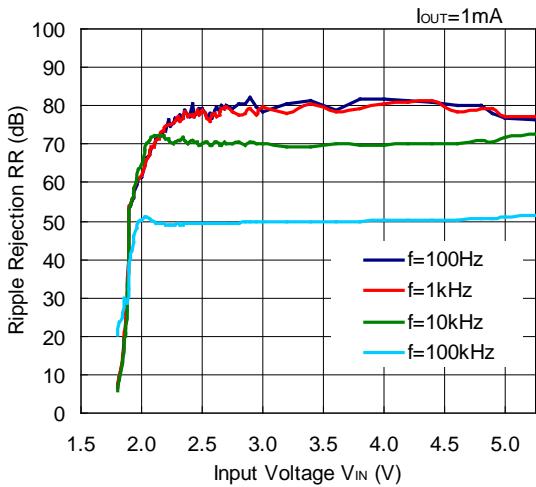
RP111x171x



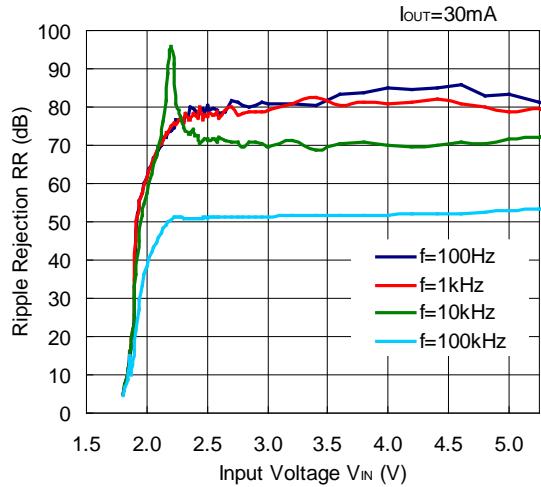
RP111x-Y

NO.EA-375-200904

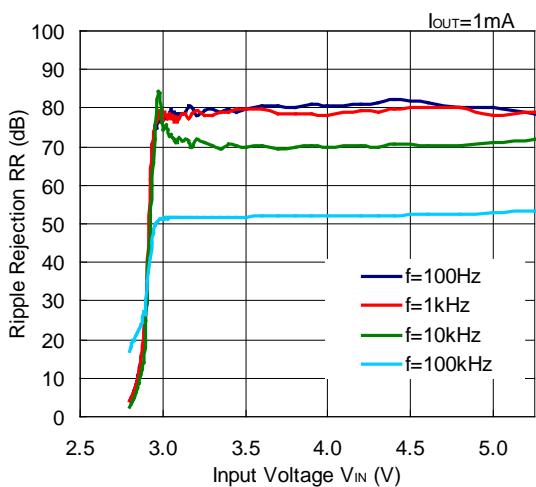
RP111x181x



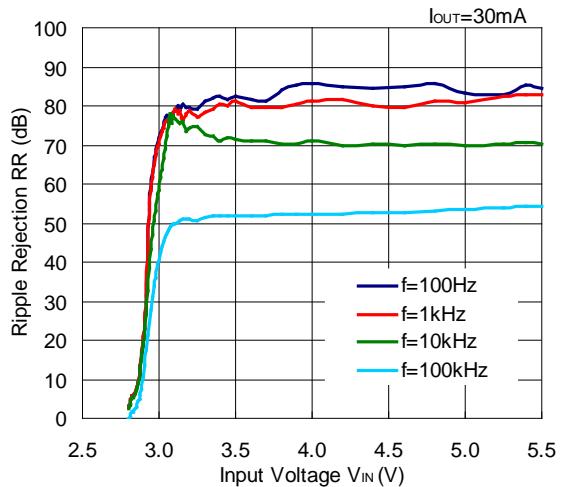
RP111x181x



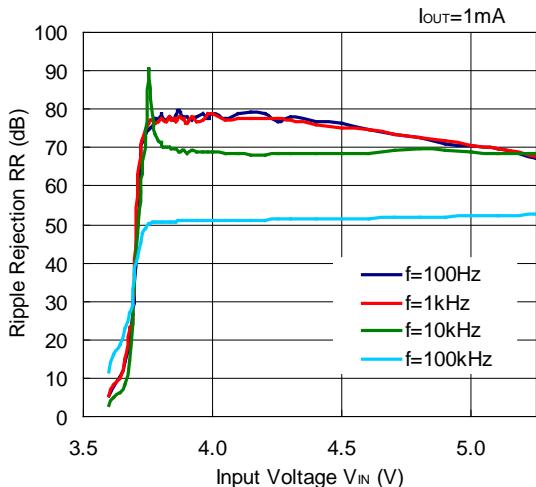
RP111x281x



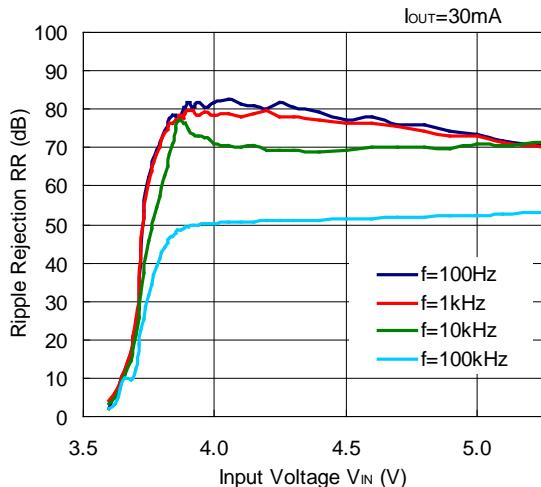
RP111x281x



RP111x361x

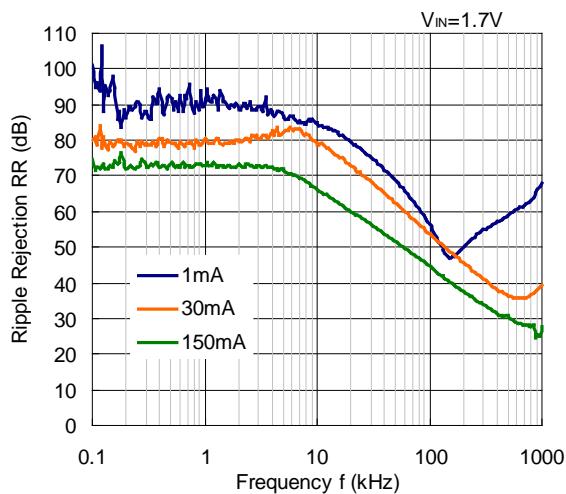


RP111x361x

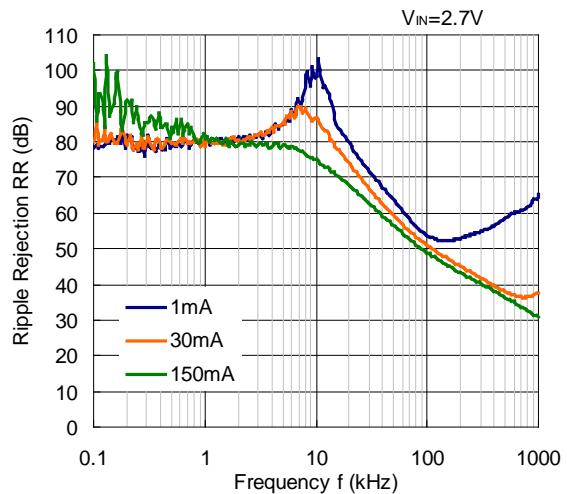


10) Ripple Rejection vs. Frequency (C1 = none, C2 = Ceramic 1.0 μ F, Ripple = 0.2 Vp-p, Ta = 25°C)

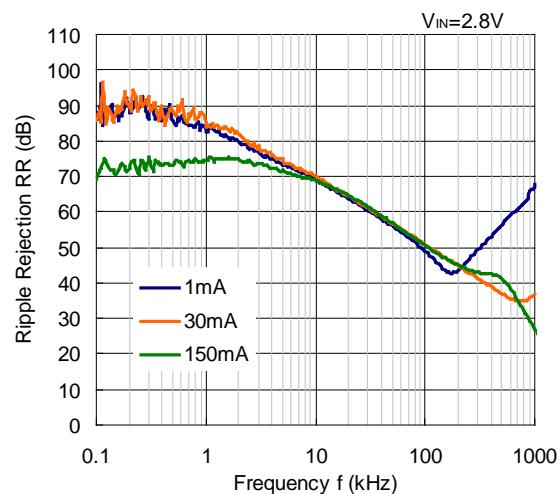
RP111x071x



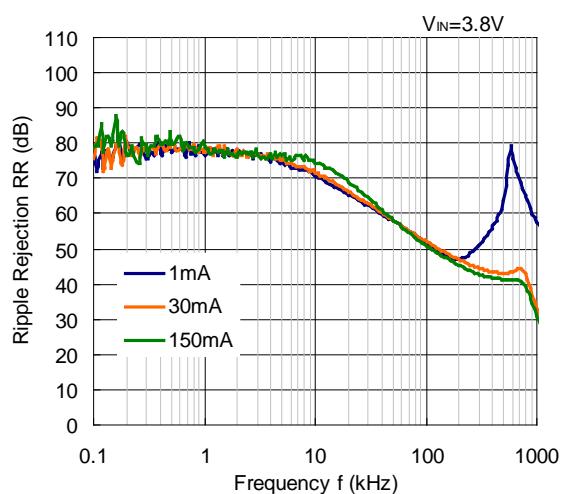
RP111x171x



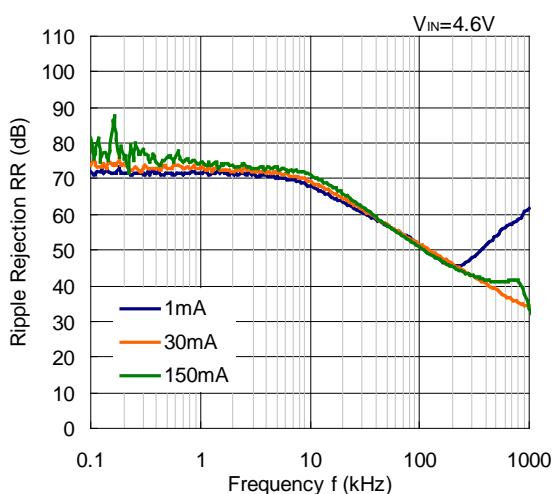
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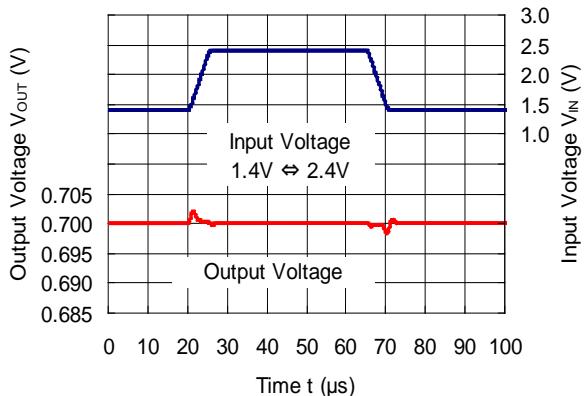
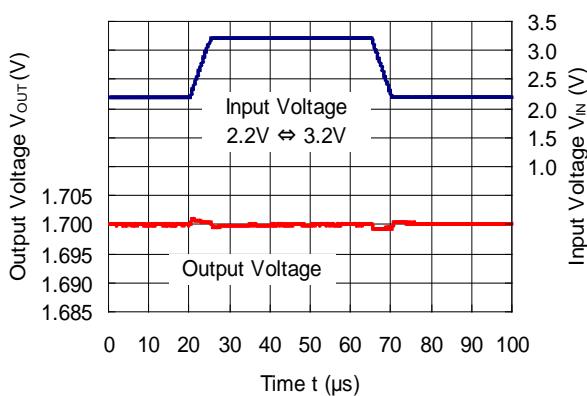
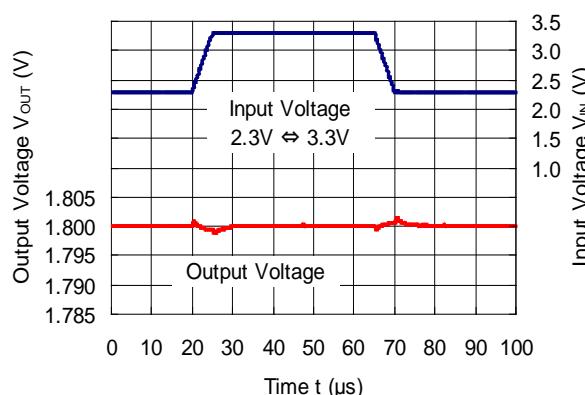
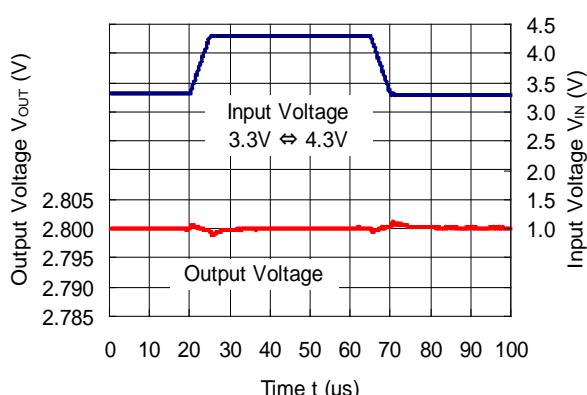
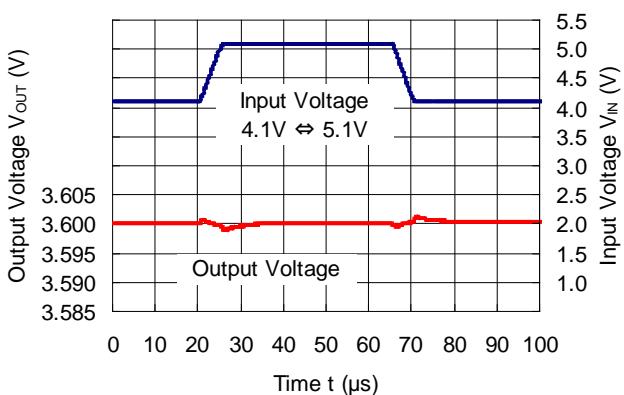


RP111x281x

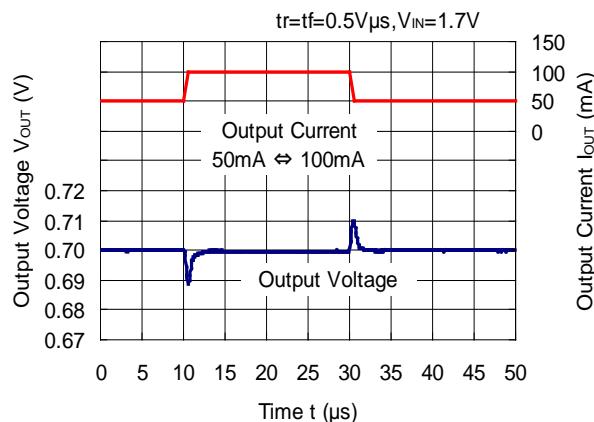
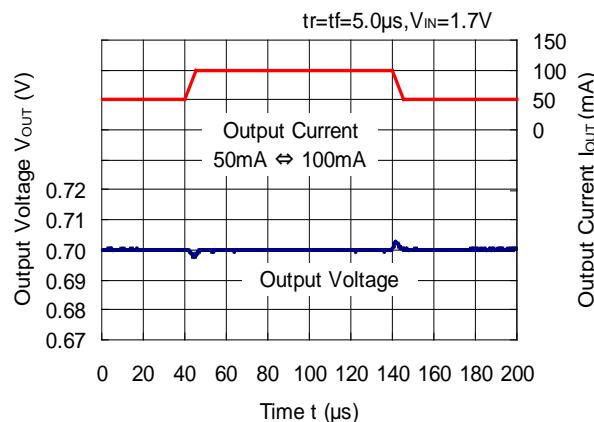
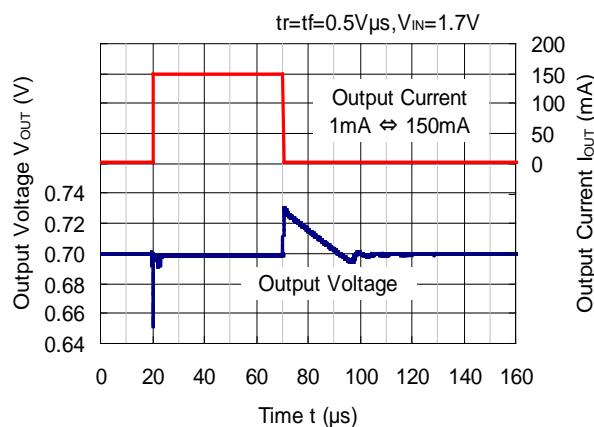
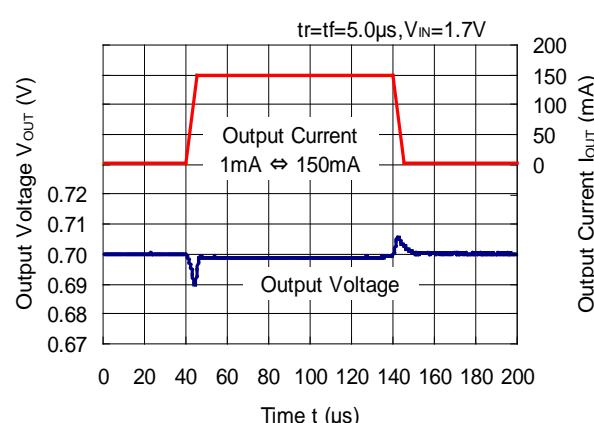
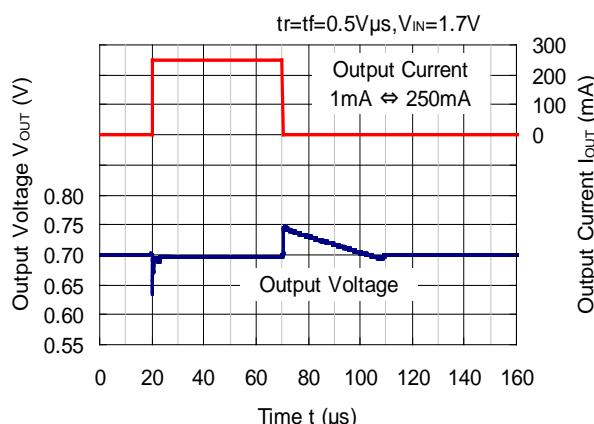
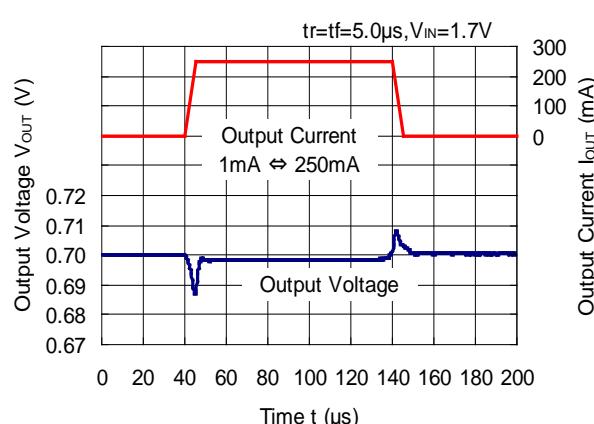


RP111x361x



11) Input Transient Response (C1= none, C2 = Ceramic 1.0 μ F, I_{OUT} = 30 mA, tr = tf = 5 μ s, Ta = 25°C)**RP111x071x****RP111x171x****RP111x181x****RP111x281x****RP111x361x**

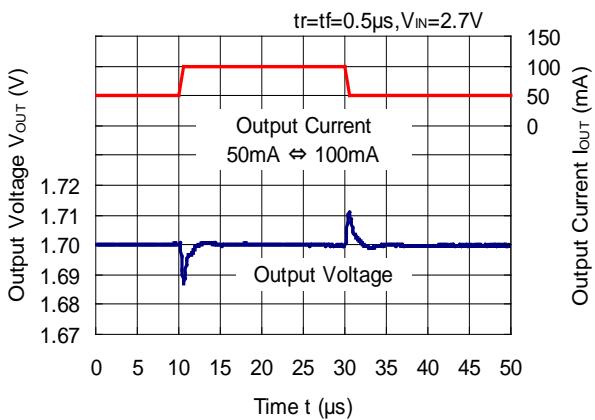
12) Load Transient Response (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, Ta = 25°C)

RP111x071x**RP111x071x****RP111x071x****RP111x071x****RP111x071x****RP111x071x**

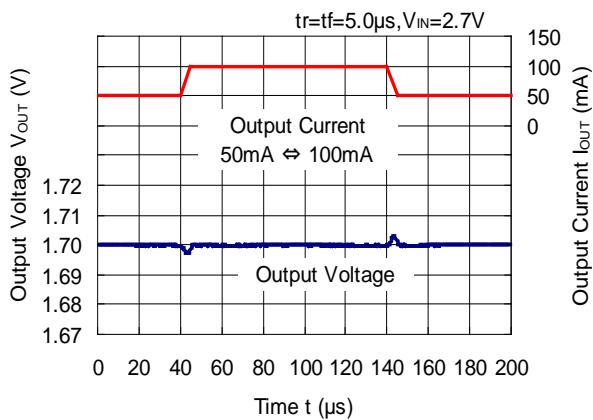
RP111x-Y

NO.EA-375-200904

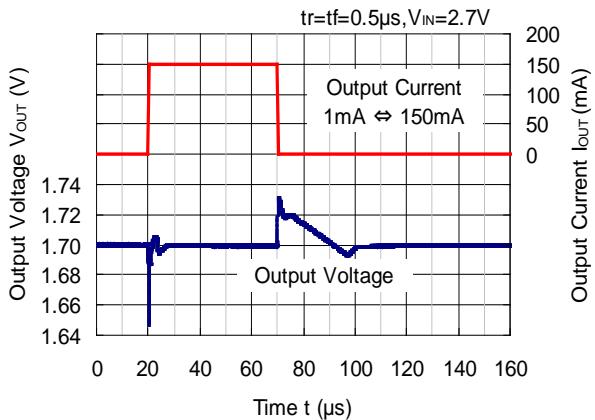
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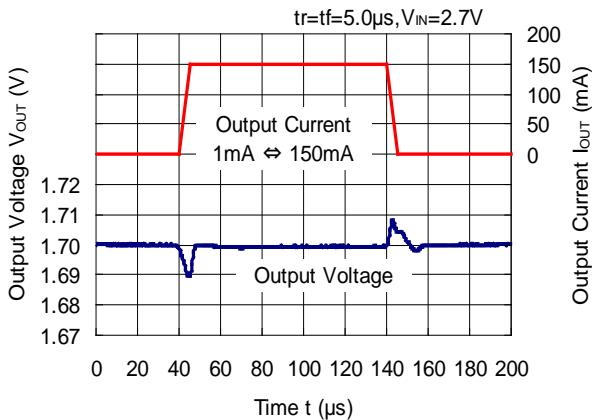
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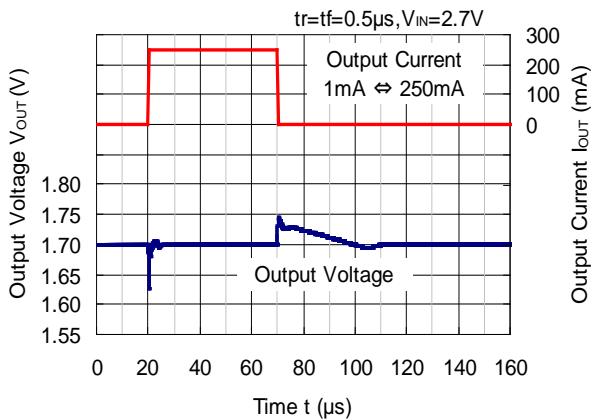
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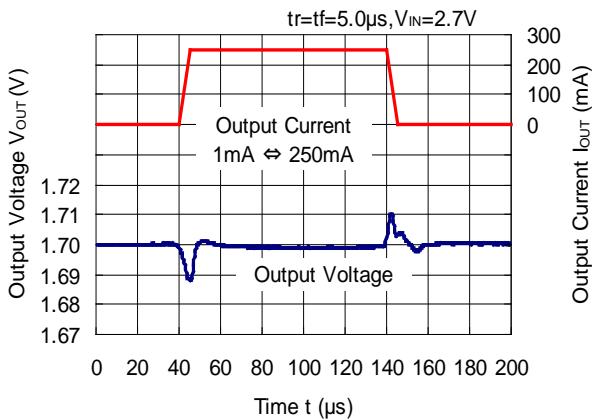
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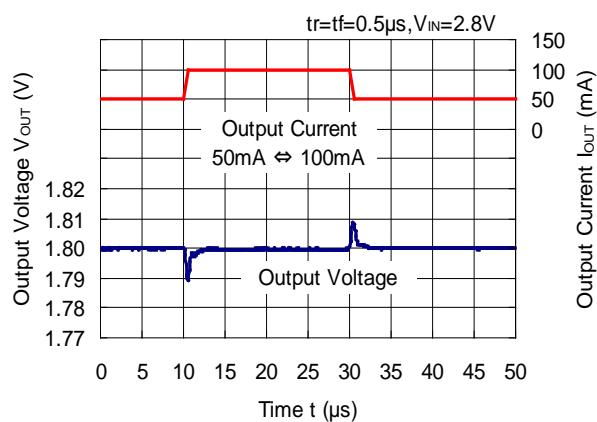
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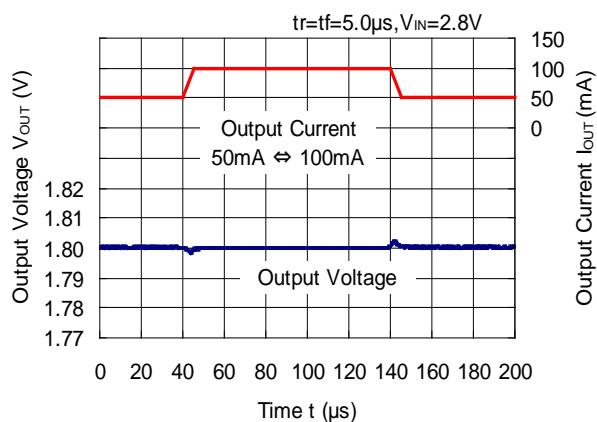
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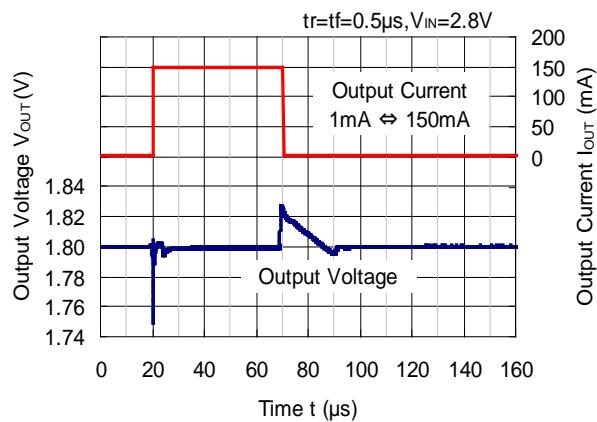
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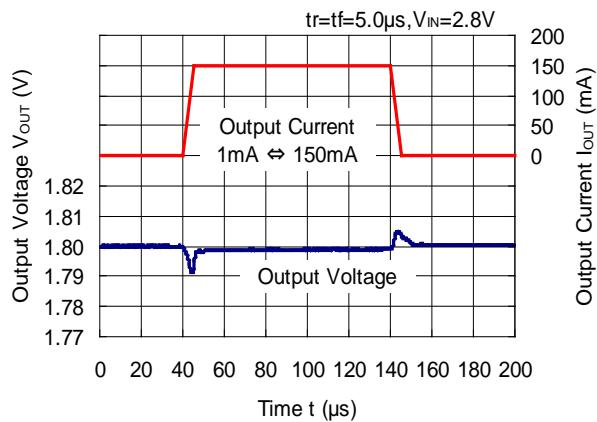
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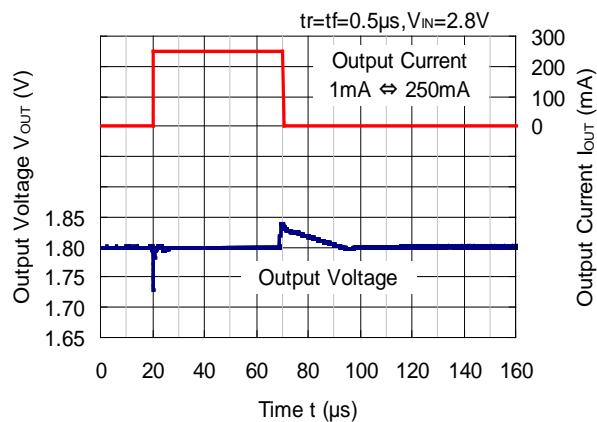
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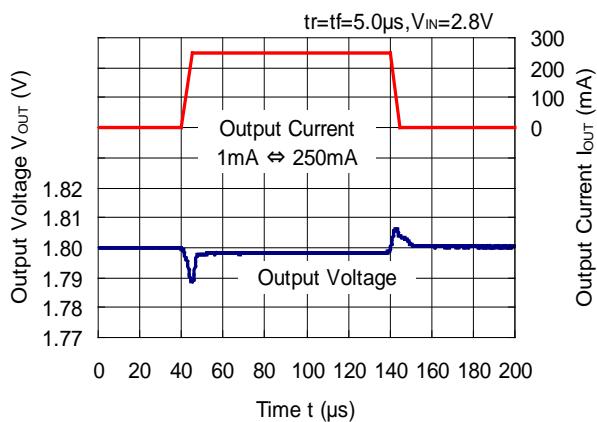
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RP111x181x



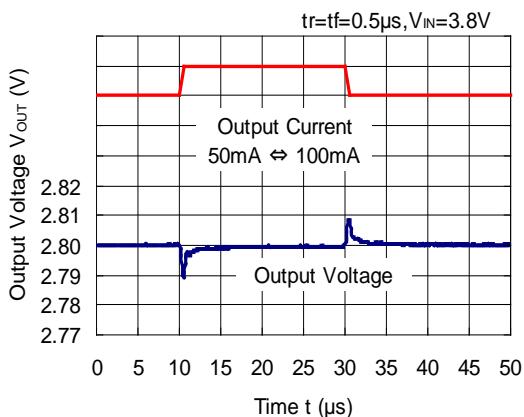
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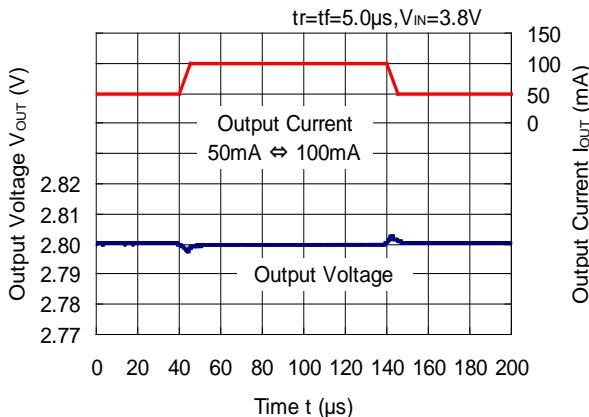
RP111x-Y

NO.EA-375-200904

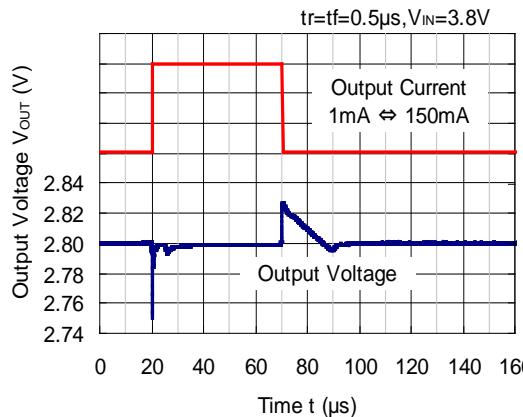
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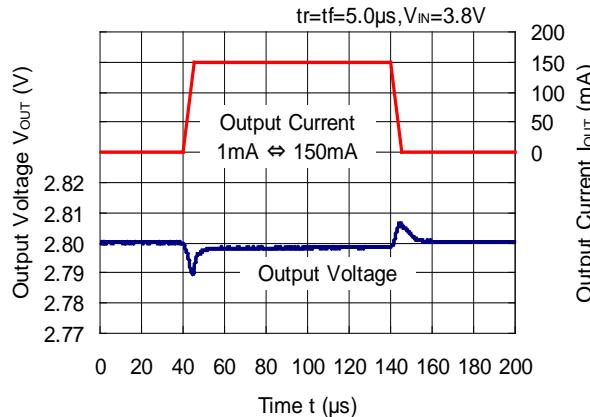
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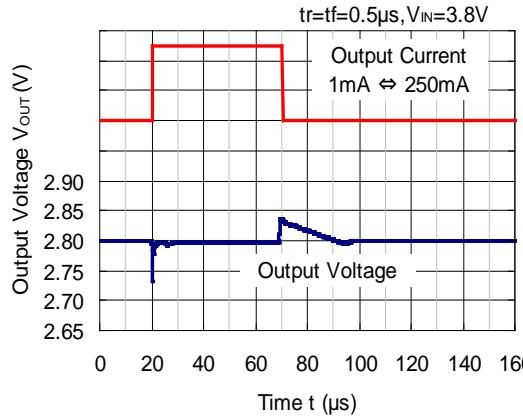
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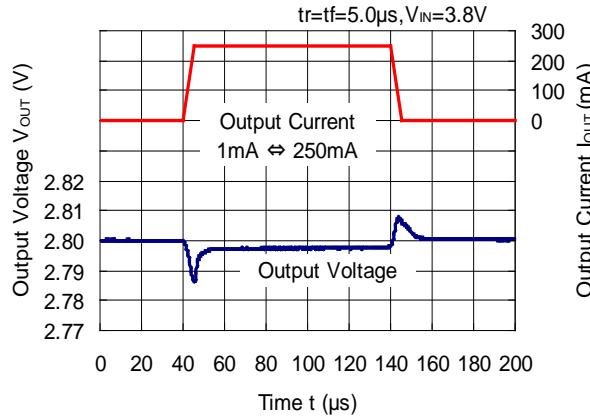
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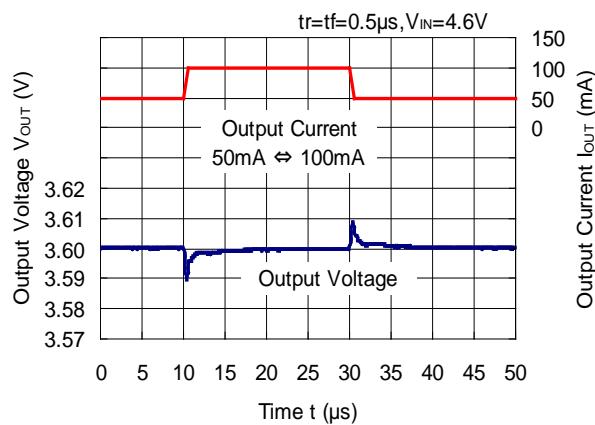
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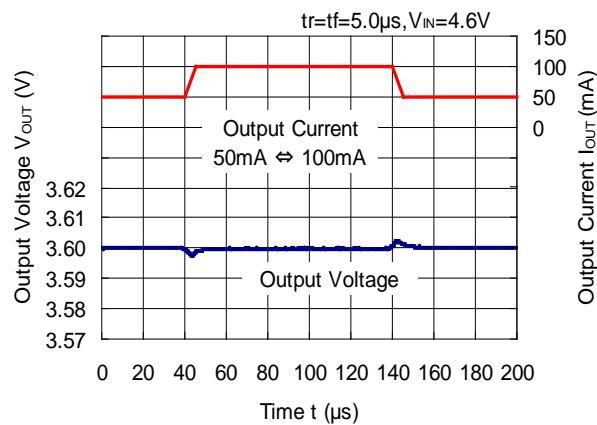
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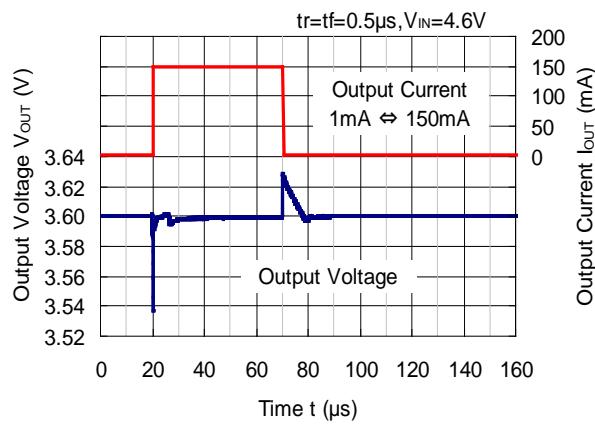
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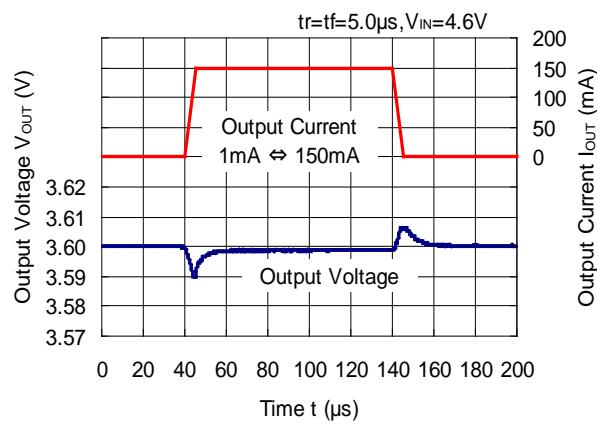
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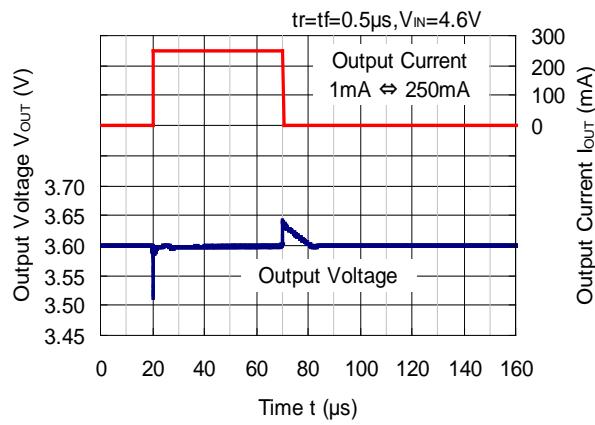
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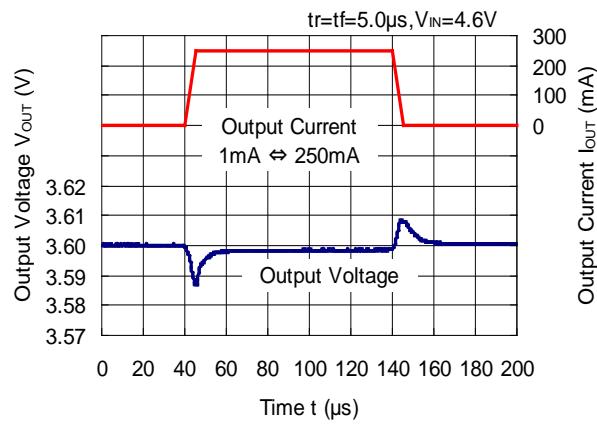
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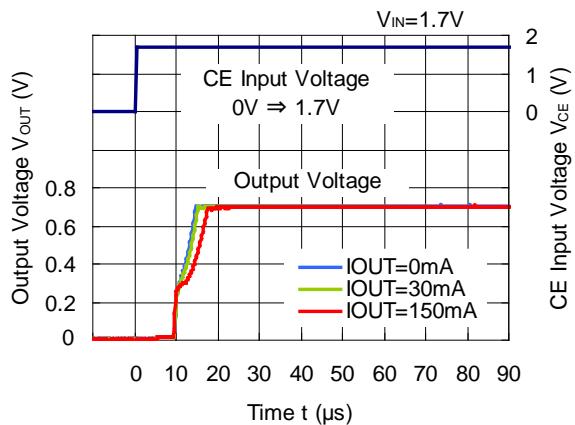
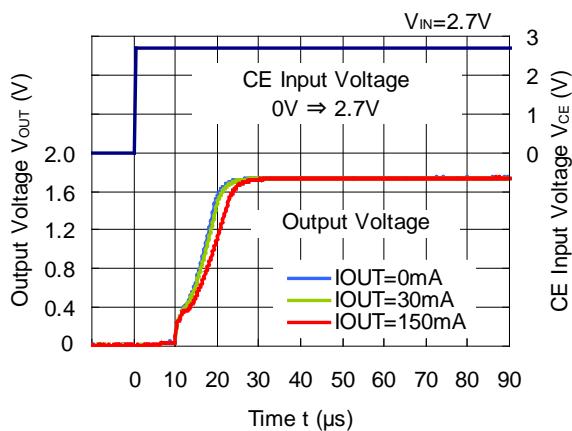
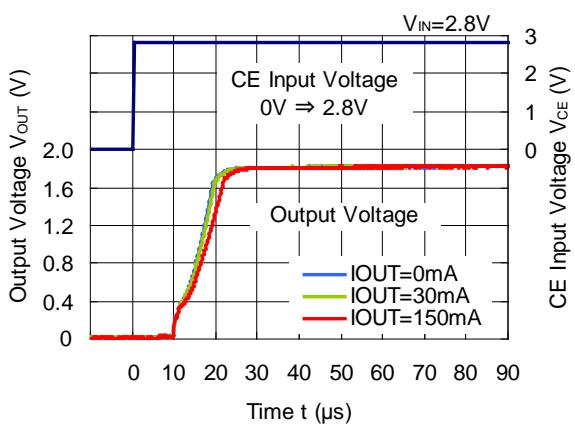
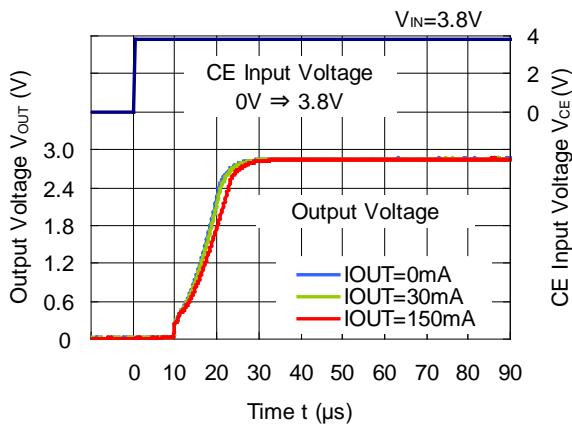
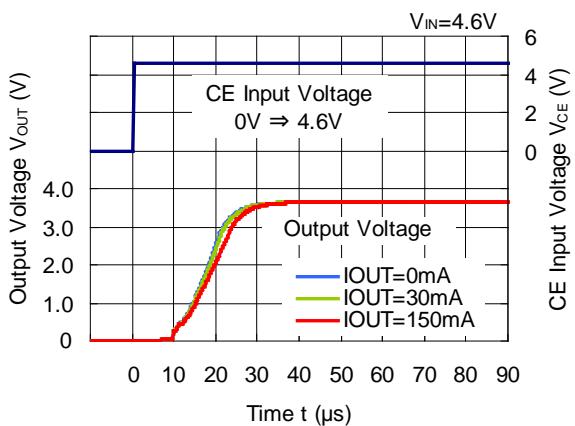


RP111x361x



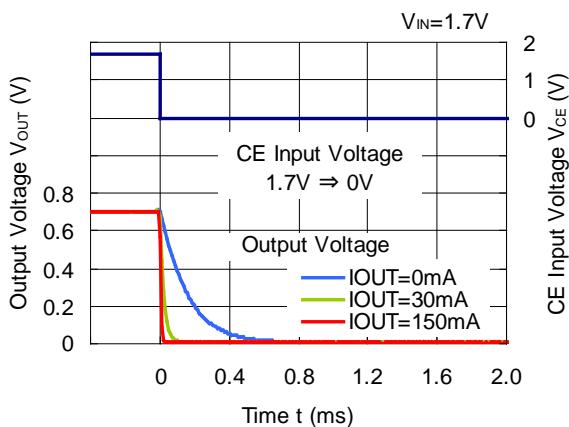
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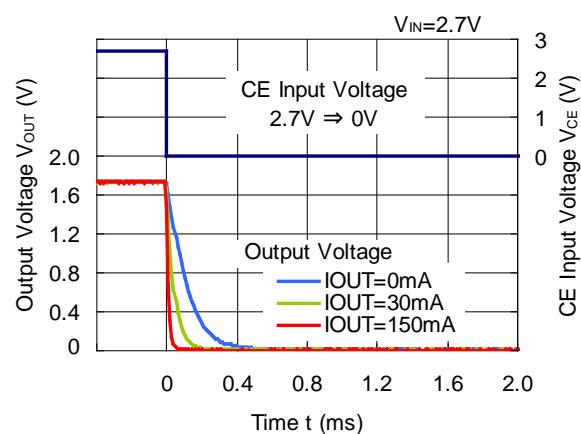
13) Turn on Speed with CE pin (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, Ta = 25°C)**RP111x071x****RP111x171x****RP111x181x****RP111x281x****RP111x361**

14) Turn off Speed with CE pin (C1 = Ceramic 1.0 μ F, C2 = Ceramic 1.0 μ F, Ta = 25°C)

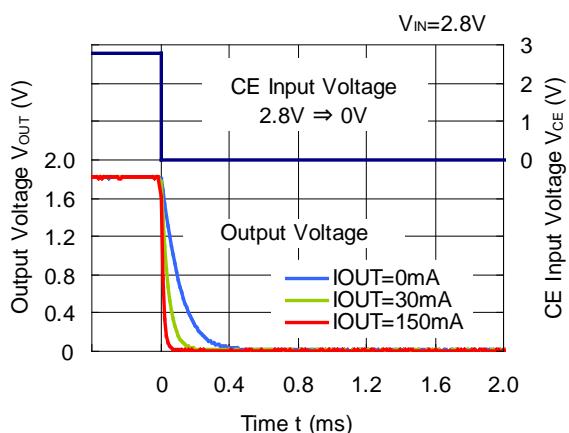
RP111x071D



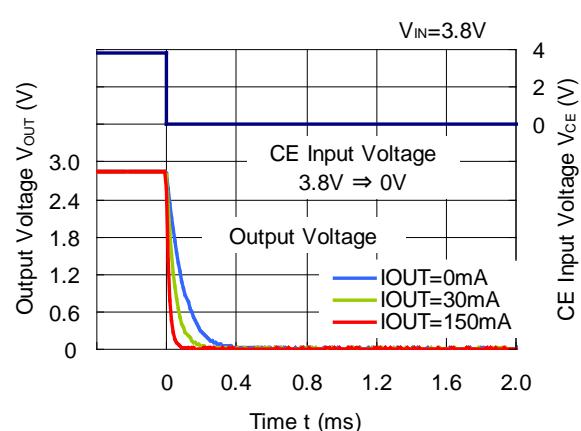
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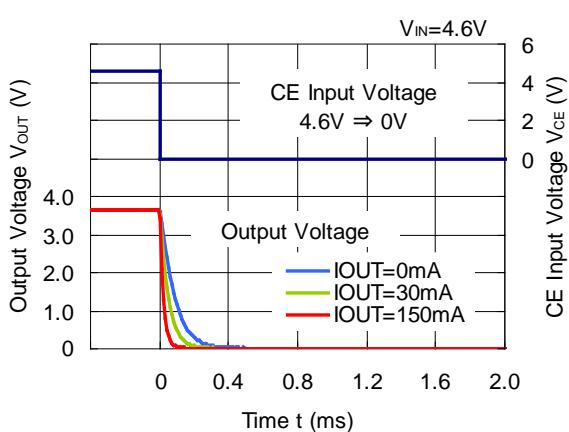
RP111x181D



RP111x281D

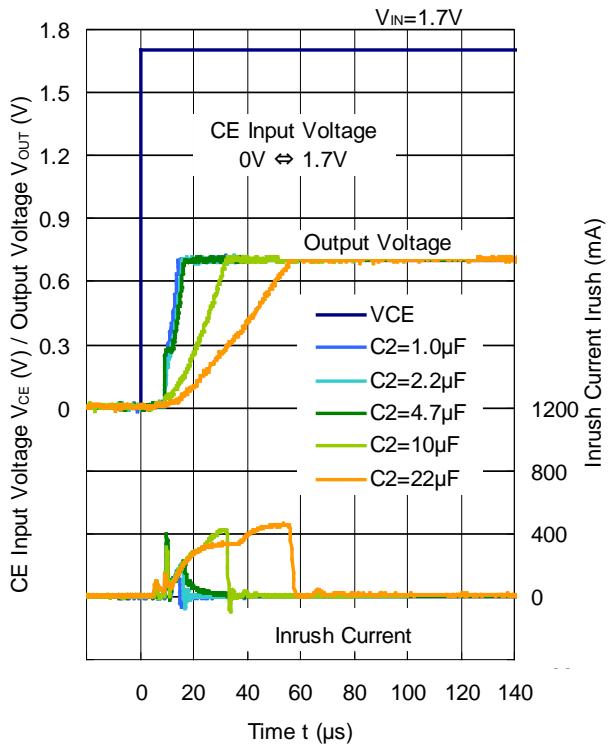


RP111x361D

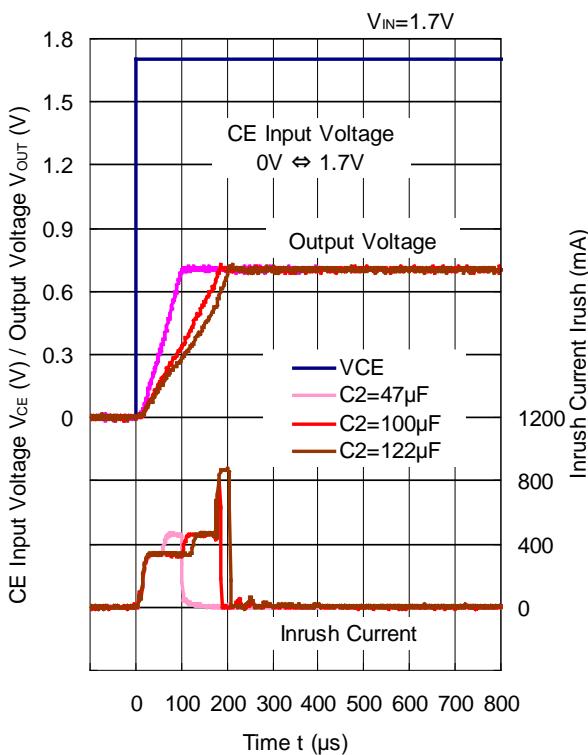


15) Inrush Current ($C_1 = \text{Ceramic } 1.0 \mu\text{F}$, $I_{\text{OUT}} = 0 \text{ mA}$, $T_a = 25^\circ\text{C}$)

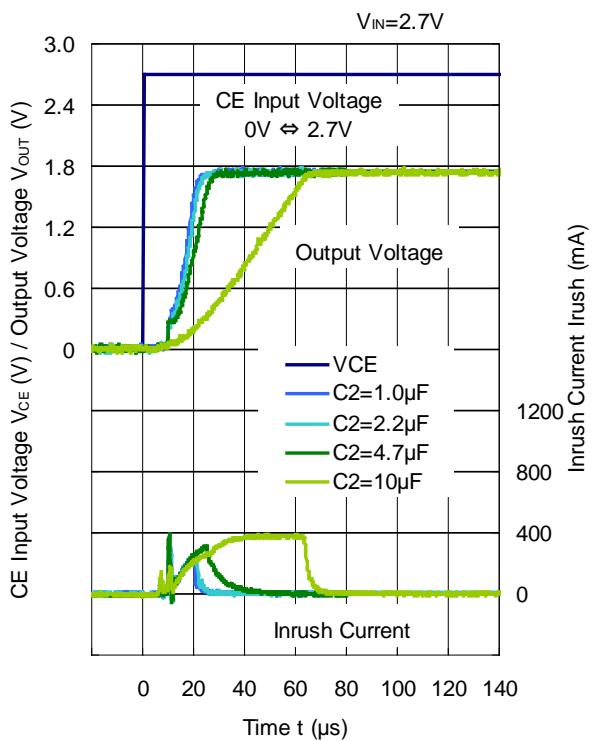
RP111x071x



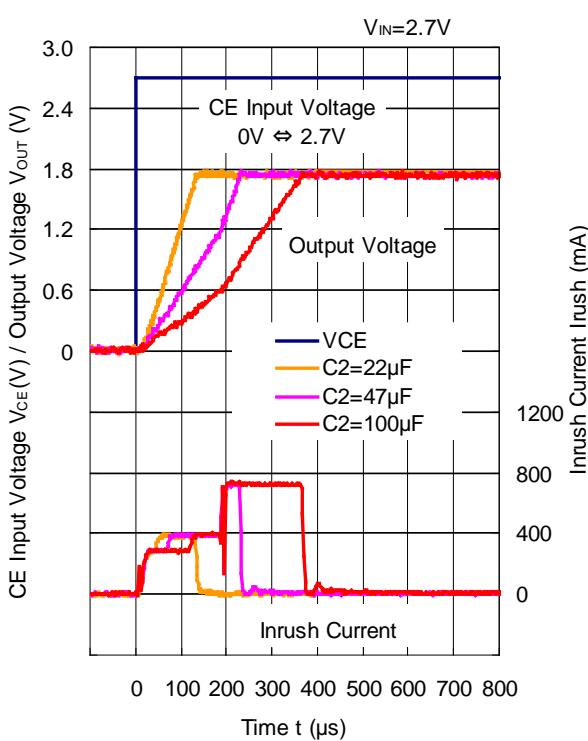
RP111x071x



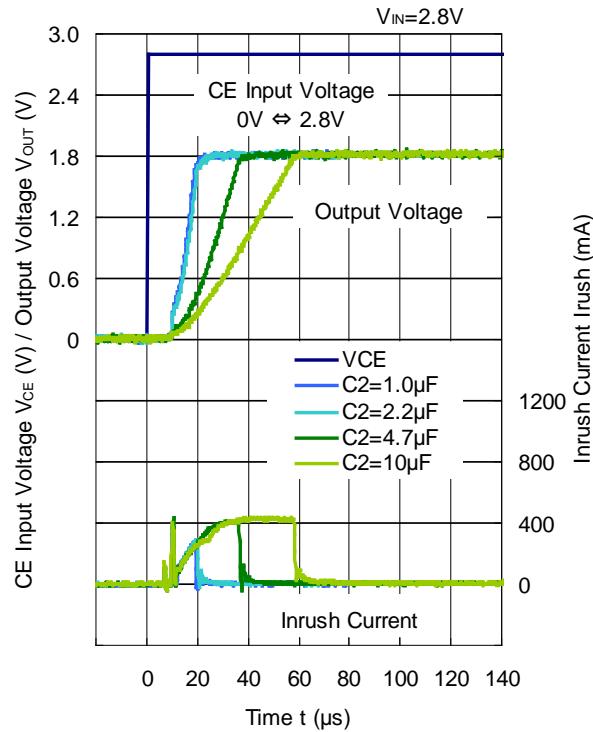
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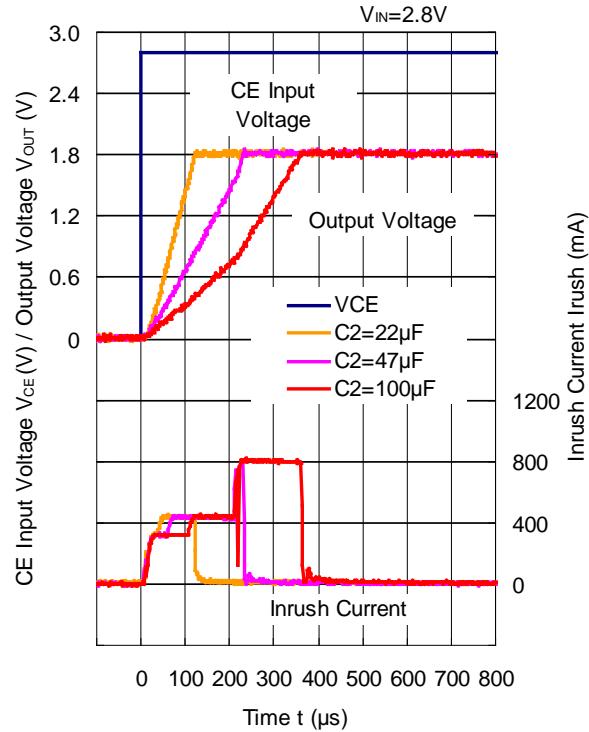
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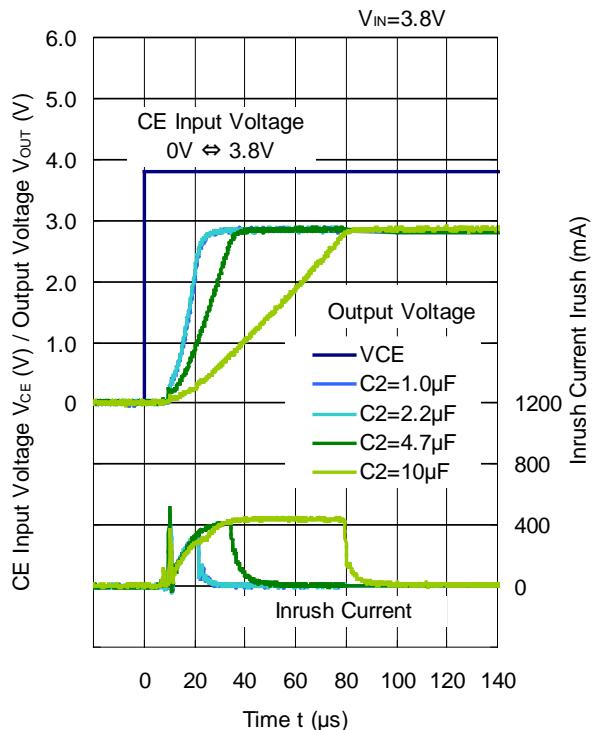
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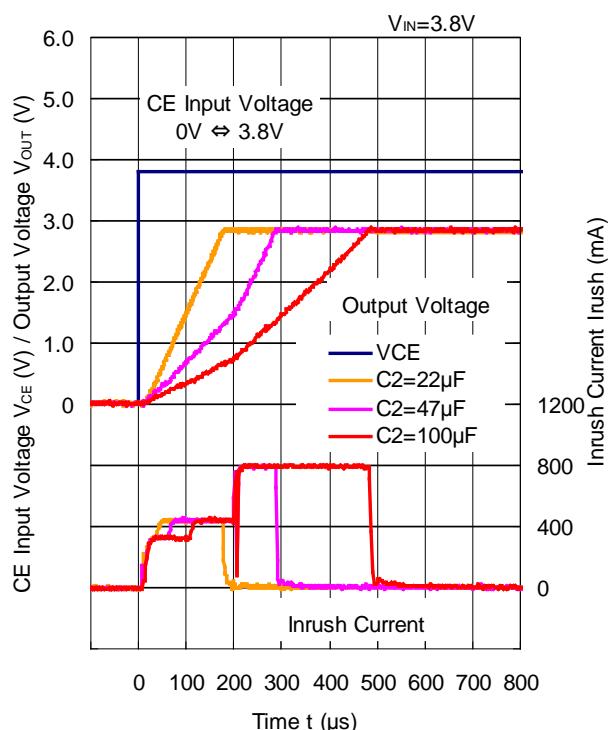
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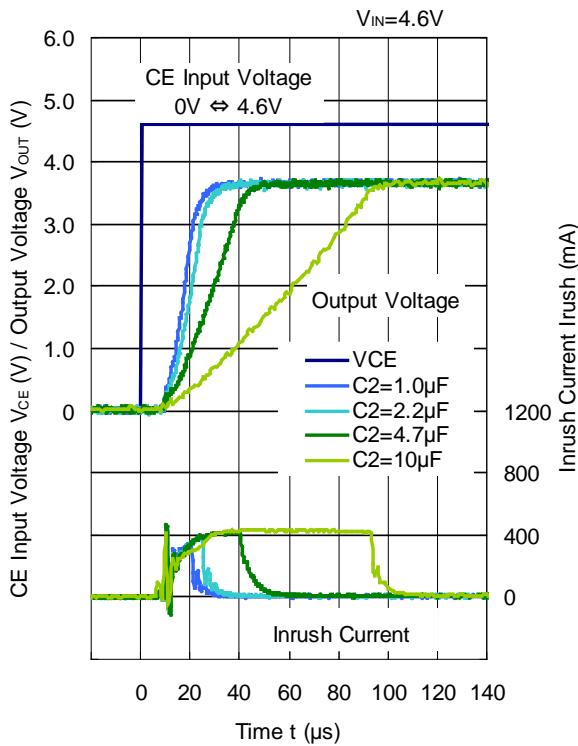
RP111x281x



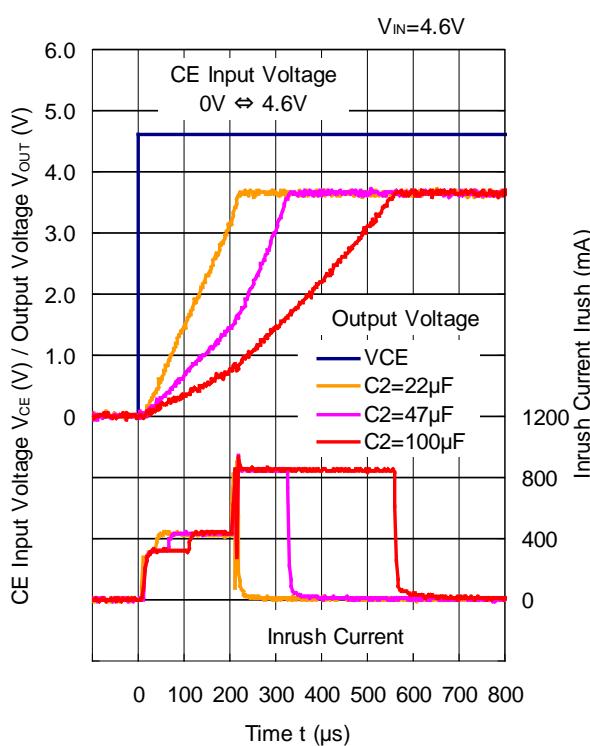
RP111x281x



RP111x361x



RP111x361x



ESR vs. Output Current

When using these ICs, consider the following points: The relations between I_{OUT} (Output Current) and ESR of an output capacitor are shown below. The conditions when the white noise level is under 40 μV (Avg.) are marked as the hatched area in the graph.

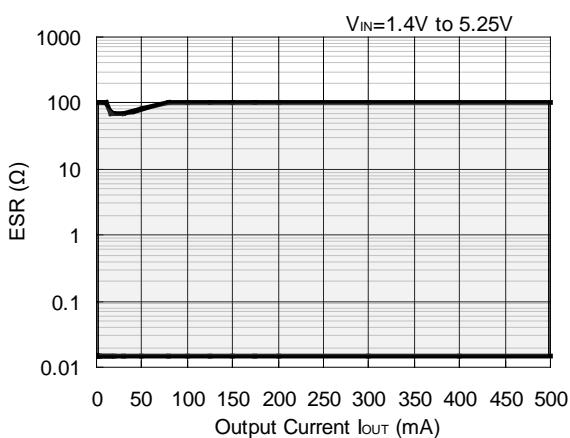
Measurement Conditions

Frequency Band: 10 Hz to 2 MHz

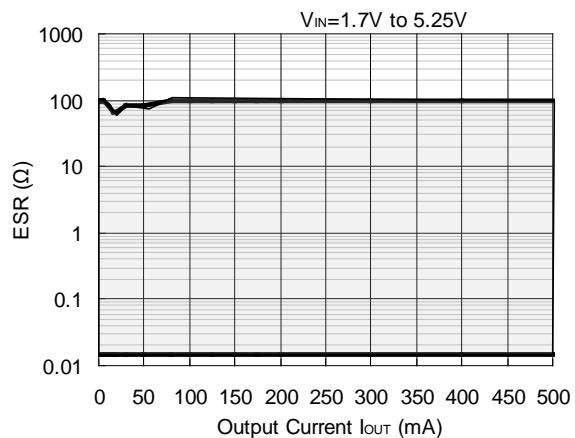
Temperature : -40°C to 85°C

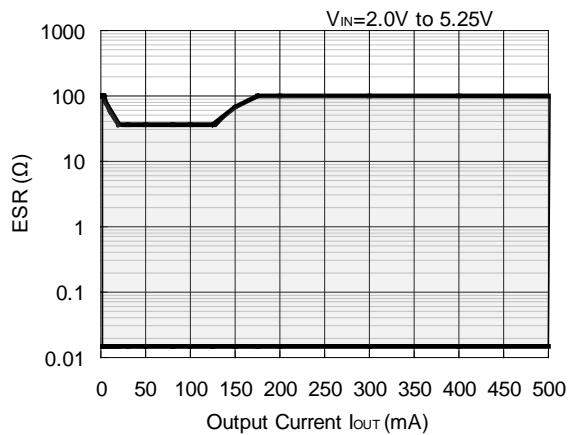
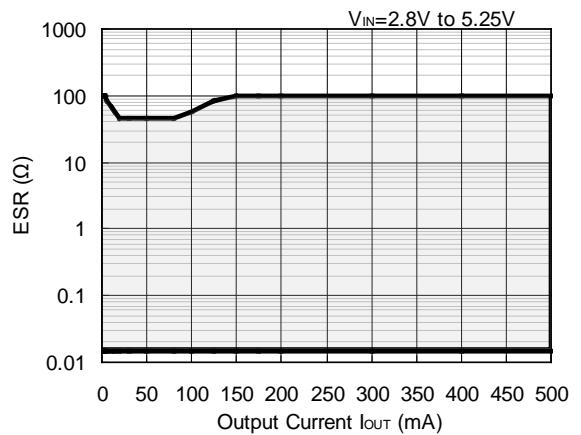
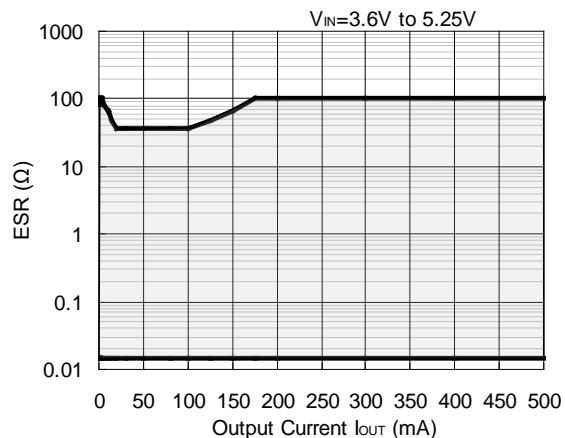
C_1, C_2 : 1.0 μF or more

RP111x071x



RP111x171x



RP111x181x**RP111x281x****RP111x361x**



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9. WLCSP products should be used in light shielded environments. The light exposure can influence functions and characteristics of the products under operation or storage.
10. There can be variation in the marking when different AOI (Automated Optical Inspection) equipment is used. In the case of recognizing the marking characteristic with AOI, please contact our sales or our distributor before attempting to use AOI.
11. Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.



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